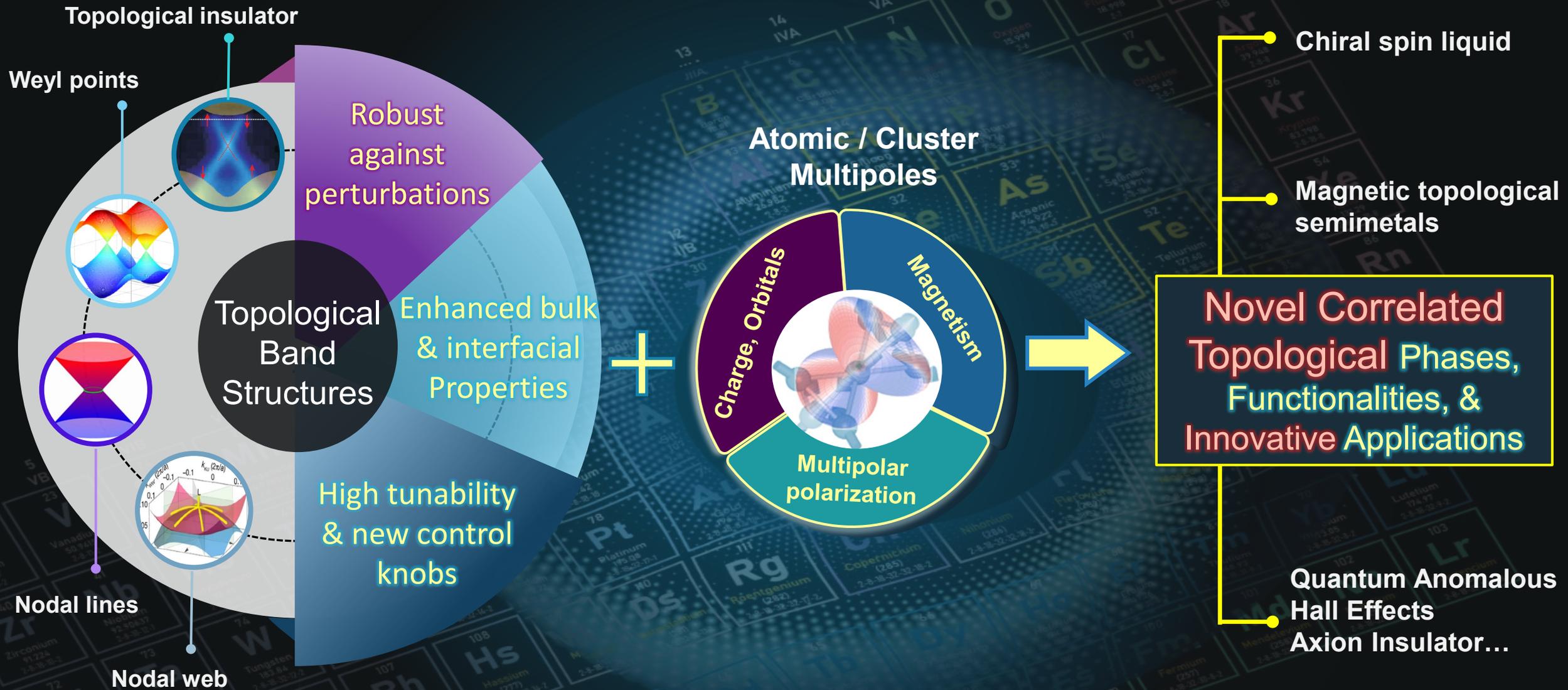


Topological and Multipolar Magnets and Spintronics

Satoru Nakatsuji

Dept. of Physics, University of Tokyo
Institute for Solid State Physics (ISSP), University of Tokyo
Institute of Quantum Matters (IQM), Johns Hopkins University

New material platforms: Blending electronic band topology with multipoles



Plan

- Multipole Physics on Correlated Electron Systems
- Topological States in Magnetic Systems
- Physics of Antiferromagnetic Weyl Semimetals
- Physics of Multipolar Kondo Lattice Systems

Plan

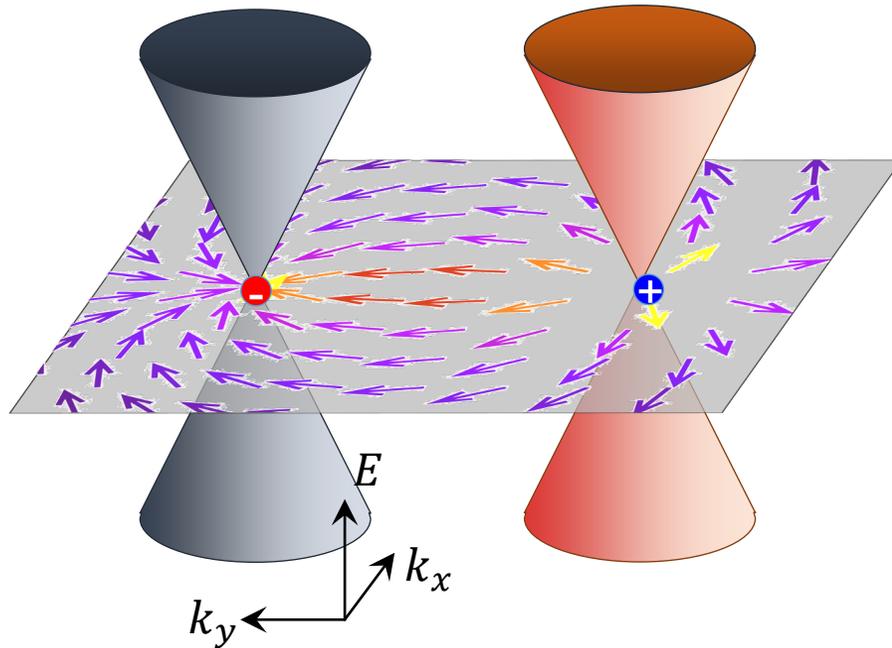
- Multipole Physics on Correlated Electron Systems
- Topological States in Magnetic Systems
- Physics of Antiferromagnetic Weyl Semimetals
- Physics of Multipolar Kondo Lattice Systems

Lecture 3

- Magnetic Weyl Semimetals
- Weyl Semimetallic State in Antiferromagnet Mn_3X
- Manipulation
 - Electrical Current Control through Spin Orbit Torque
- Quantum Coherent Transport
 - Tunneling Magnetoresistances

Weyl Semimetal State

X. Wan, A. M. Turner, A. Vishwanath, and S. Y. Savrasov, 2011



**Topological Metal with
broken spatial inversion/
time reversal symmetry.**

**Pair of Linearly dispersive excitation
Similar to Graphene, but in 3D.**

Weyl Eq. $\mathcal{H} = \sum_{i=1}^3 \mathbf{v}_i \cdot \mathbf{k} \sigma_i$

**Robust against Symm. Breaking
perturbation**

Crossing points:

Magnetic Monopoles

**Source and sink of Berry curvature/
Fictitious Field**

- **Layered Quantum Hall Effect**
- **Chiral Anomaly**

Chern number for a single Weyl point

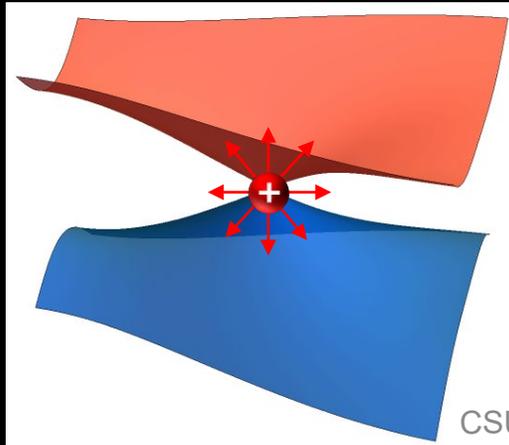
$$\gamma \vec{p} \vec{\sigma} |\psi\rangle = E |\psi\rangle \quad \text{Weyl Equation}$$

→ Same as magnetic monopole in real space! $H = \frac{1}{2} \vec{B} \vec{\sigma}$

□ Eigen energies: $E = \pm |\vec{p}|$

□ Eigen states: $|\psi_+\rangle = \begin{pmatrix} e^{-i\phi} \cos \theta/2 \\ \sin \theta/2 \end{pmatrix}$ $|\psi_-\rangle = \begin{pmatrix} -e^{-i\phi} \sin \theta/2 \\ \cos \theta/2 \end{pmatrix}$

□ Berry curvature: $\Omega_k = \mp \gamma \frac{\vec{p}}{2p^3}$



e.g. for $\gamma = -1$,

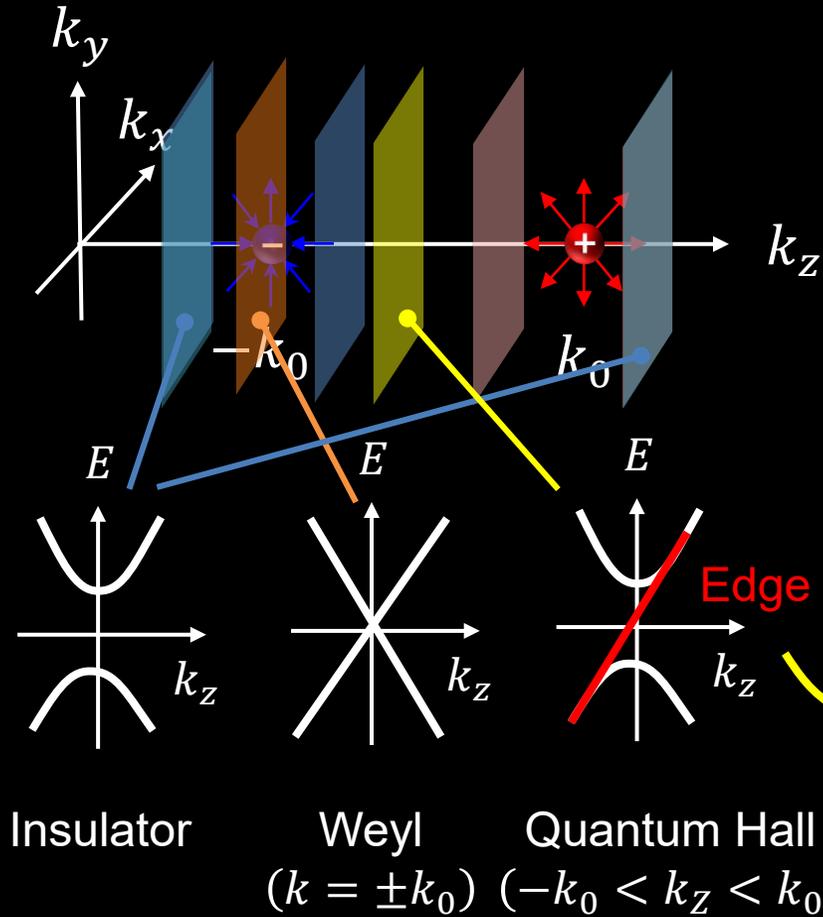
□ Chern number

$$C = \frac{\int \Omega_k dS}{2\pi} = +1$$

□ monopole charge

$$Q = \frac{C}{2} = +1/2$$

A pair of Weyl points

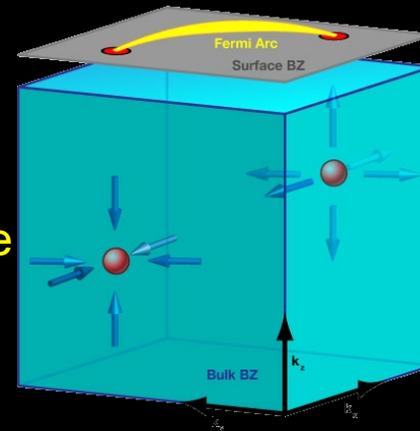


To satisfy the Gauss's theorem,

$$C = \begin{cases} 1 & (-k_0 < k_z < k_0) \\ 0 & (k_z < -k_0, k_0 < k_z) \end{cases}$$

→ k_x - k_y plane at $-k_0 < k_z < k_0$ can be regarded as the quantum Hall system.

Surface state (Fermi arc)

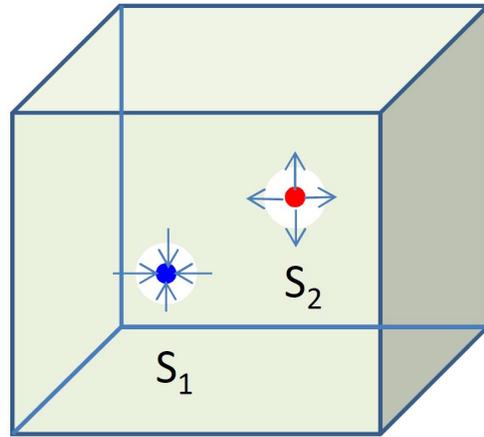


□ Hall conductivity

$$\sigma_{xy} = -\frac{e^2}{(2\pi)^2 \hbar} \int_{-k_0}^{k_0} 1 dk_z = -\frac{e^2}{(2\pi)^2 \hbar} (2k_0)$$

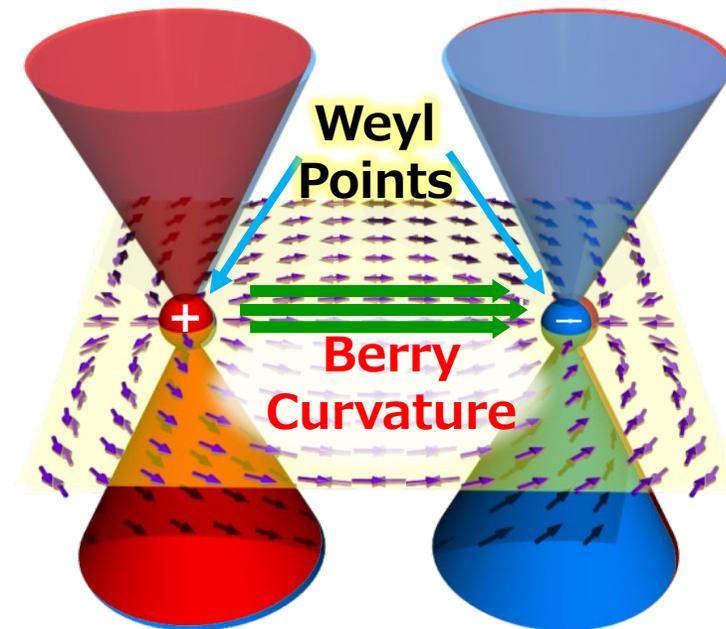
Nielsen-Ninomiya theorem 1983

- Bloch Bands in 3D Brillouin Zone

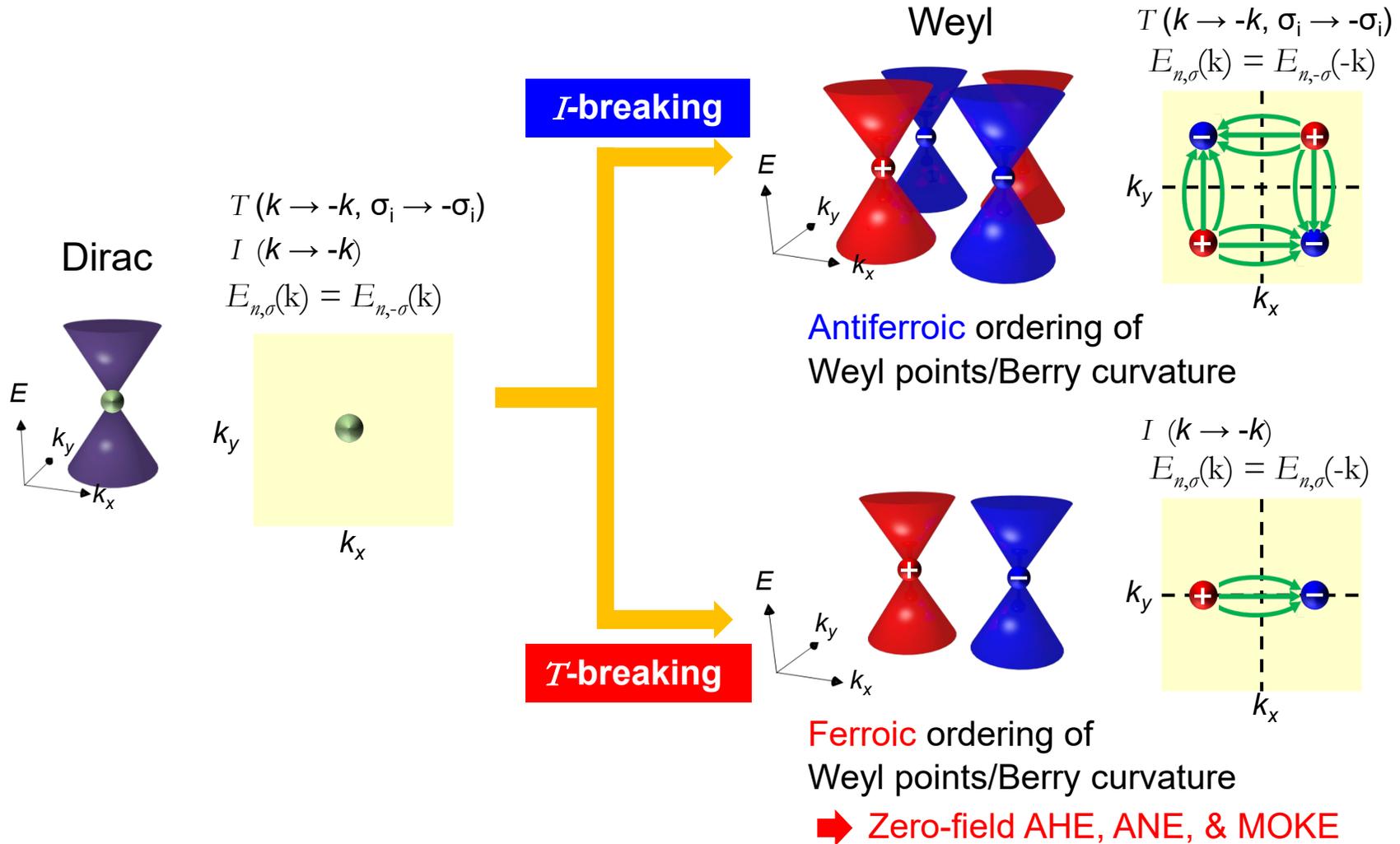


Weyl nodes appears in pair with opposite chiralities

- Sign of a monopole charge depends on band- n and chiralities



Weyl Nodes and Symmetry

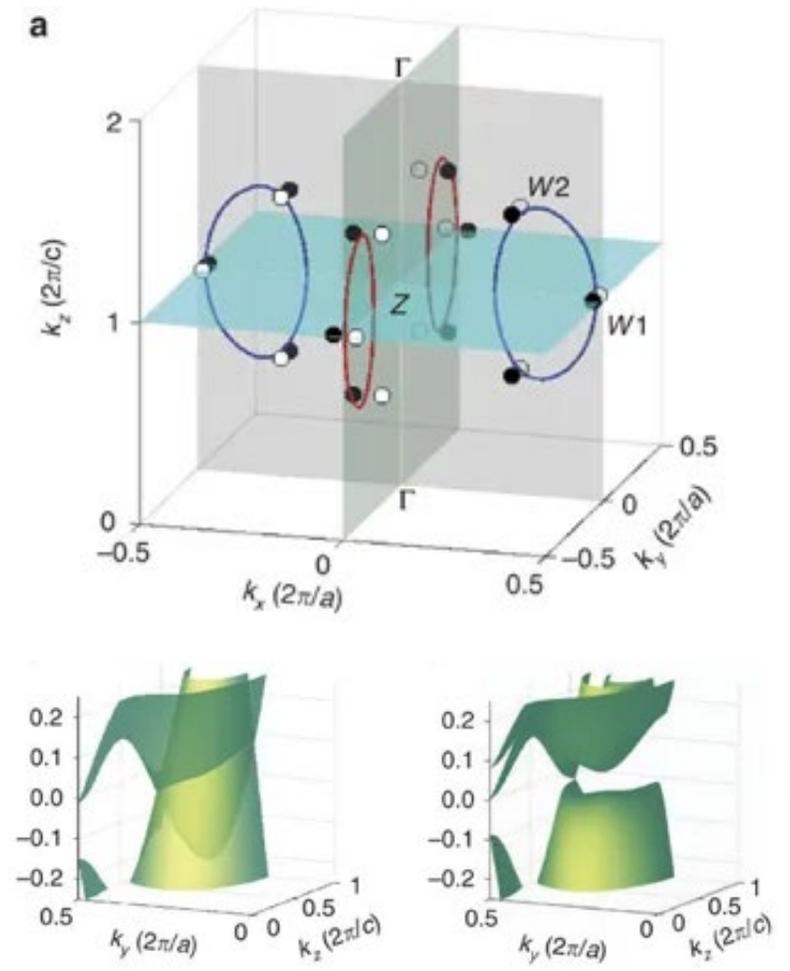
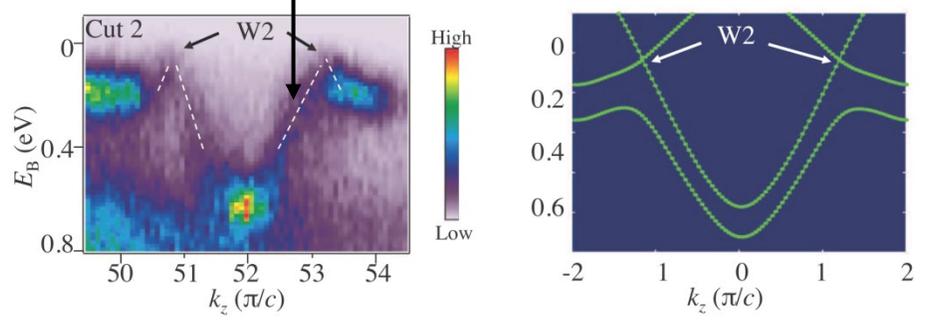
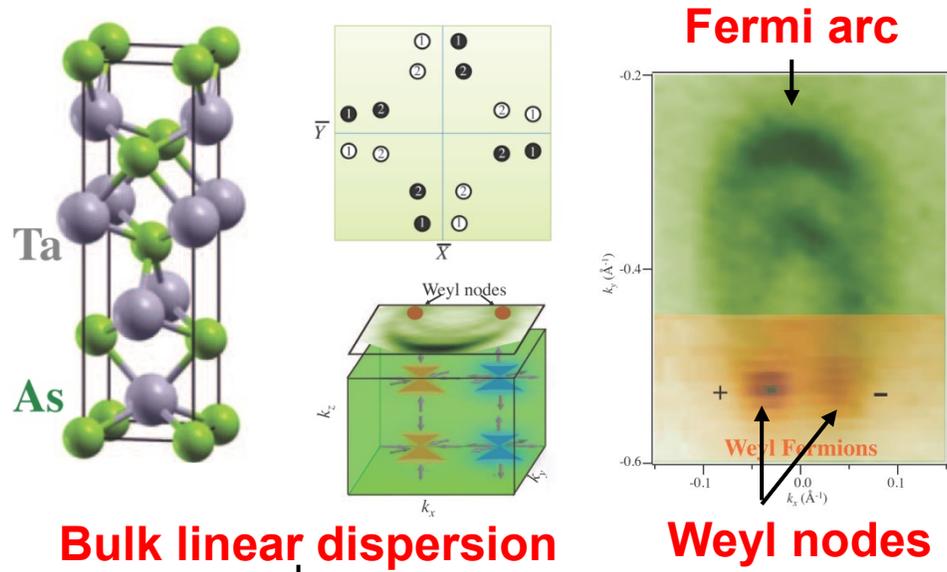


T-breaking Weyl semimetal = Weyl magnet has non-zero Berry curvature

showing large zero-field electrical, thermal, & optical responses

I-breaking Weyl semimetal: TaAs

ARPES (Angle resolved photoemission spectroscopy)



Xu *et al.*, Science **349**, 613 (2015); Lv *et al.*, PRX **5**, 031013 (2015).

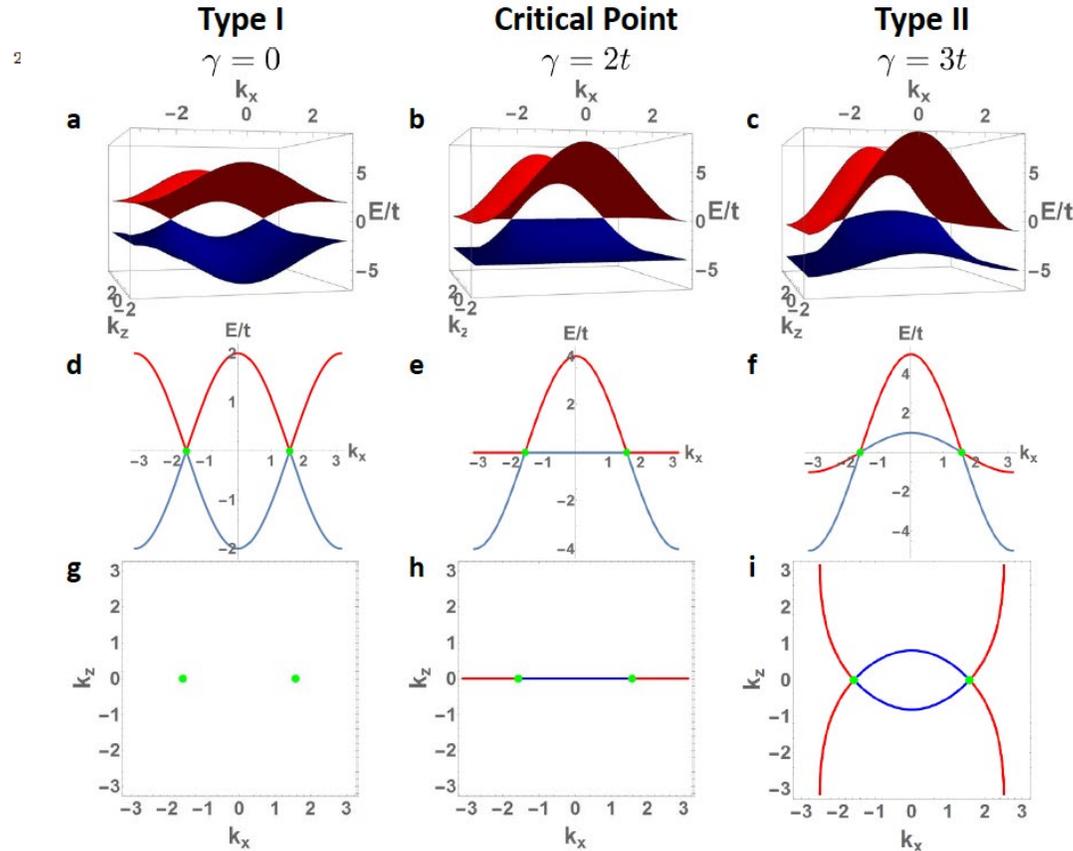
Huang *et al.*, Nat. Com. (2016)

Type II Weyl semi metal

Minimal models for topological Weyl semimetals

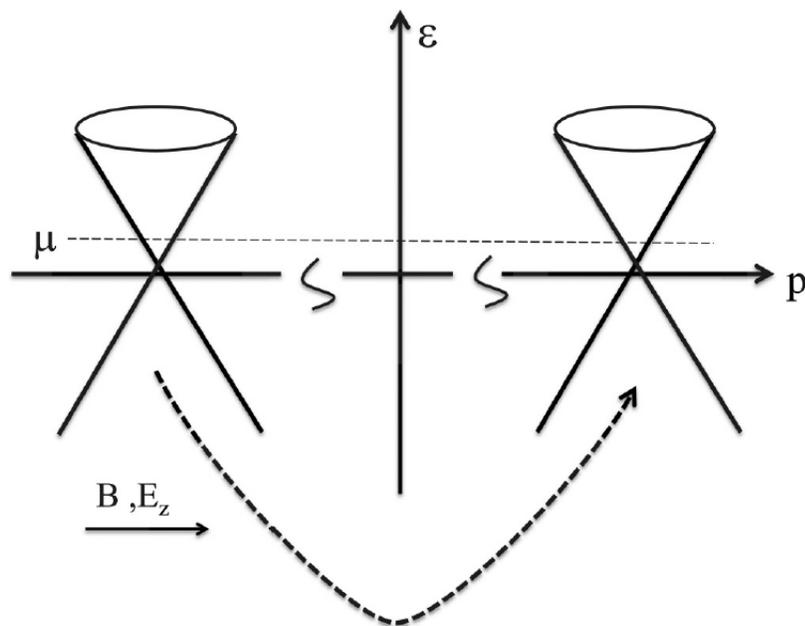
Phys. Rev. B **95** 075133 2017.

Timothy M. McCormick,^{1,*} Itamar Kimchi,^{2,†} and Nandini Trivedi^{1,‡}

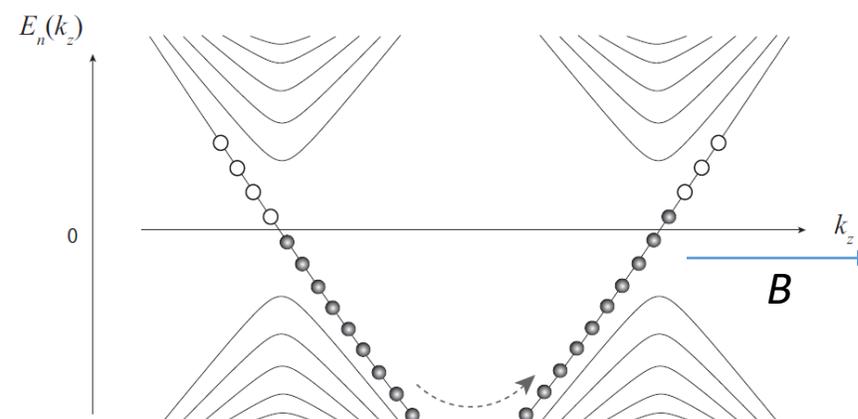


$$\hat{\mathcal{H}}_A^{\text{TRB}}(\mathbf{k}) = \gamma(\cos(k_x) - \cos(k_0))\hat{\sigma}_0 - (m(2 - \cos(k_y) - \cos(k_z)) + 2t_x(\cos(k_x) - \cos(k_0)))\hat{\sigma}_1 + 2t_y \sin(k_y)\hat{\sigma}_2 + 2t_z \sin(k_z)\hat{\sigma}_3 \quad (8)$$

Chiral Anomaly: Weyl Fermions



Fukushima, Kharzeev, and Warringa
 Phys. Rev. D 2008
 Li et al, Nature Phys 2016



$n = 0$ Landau Level

$$\sigma_{zz} = \frac{e^2}{4\pi^2\hbar c} \frac{v (eB)^2 v^2}{\mu^2} \tau.$$

Strongly Anisotropic Magnetoconductance
 Only when $E//B$, Positive Magnetoconductance

Chiral Anomaly: Weyl Fermions

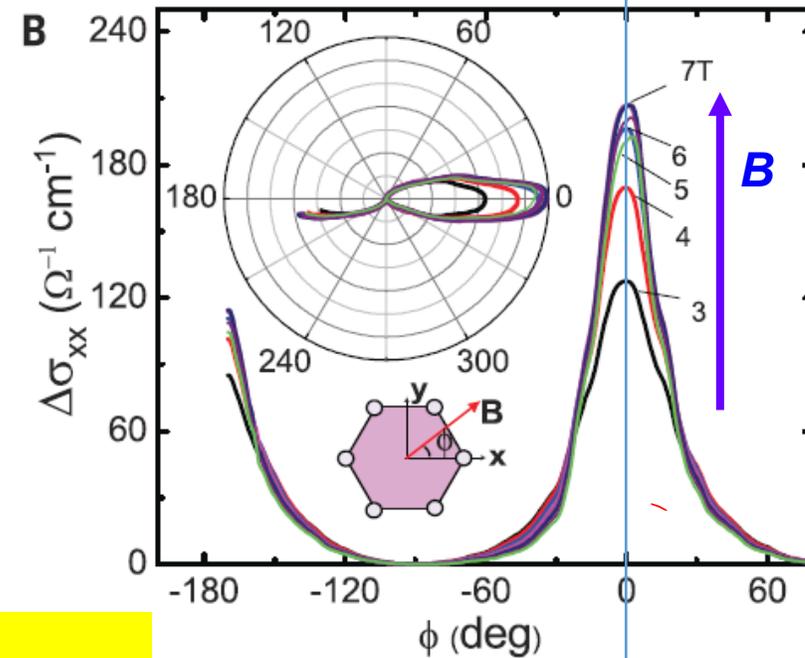
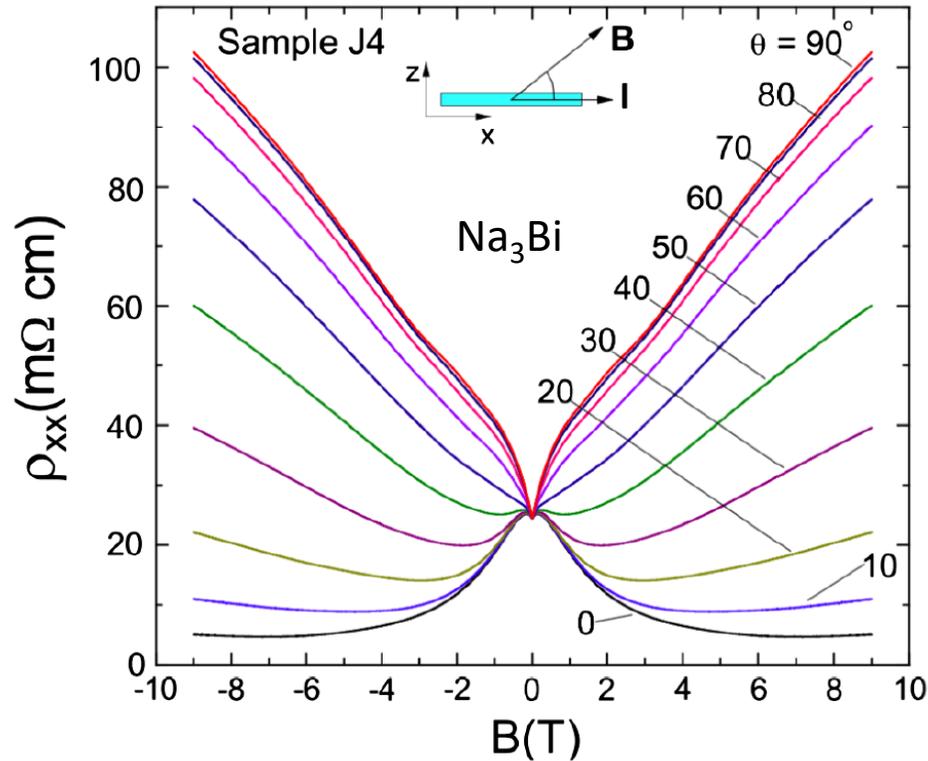
RESEARCH | REPORTS

Science 2015

TOPOLOGICAL MATTER

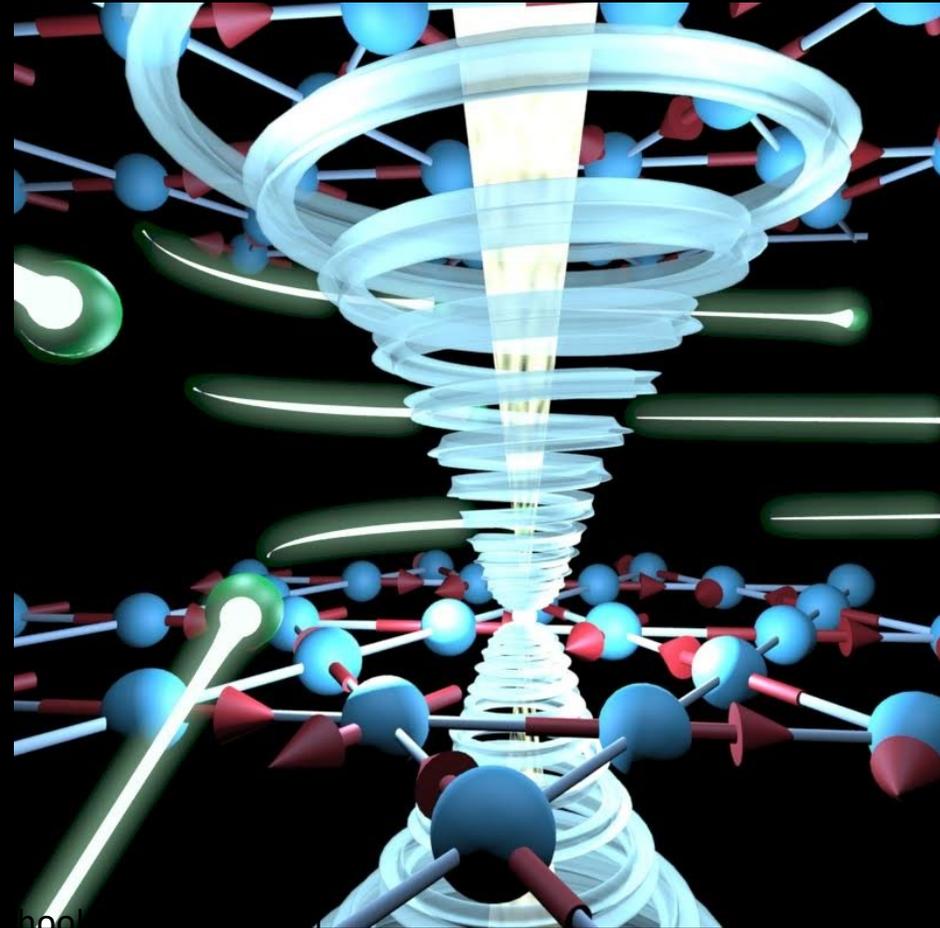
Evidence for the chiral anomaly in the Dirac semimetal Na_3Bi

Jun Xiong,¹ Satya K. Kushwaha,² Tian Liang,¹ Jason W. Krizan,² Max Hirschberger,¹ Wudi Wang,¹ R. J. Cava,² N. P. Ong^{1*}



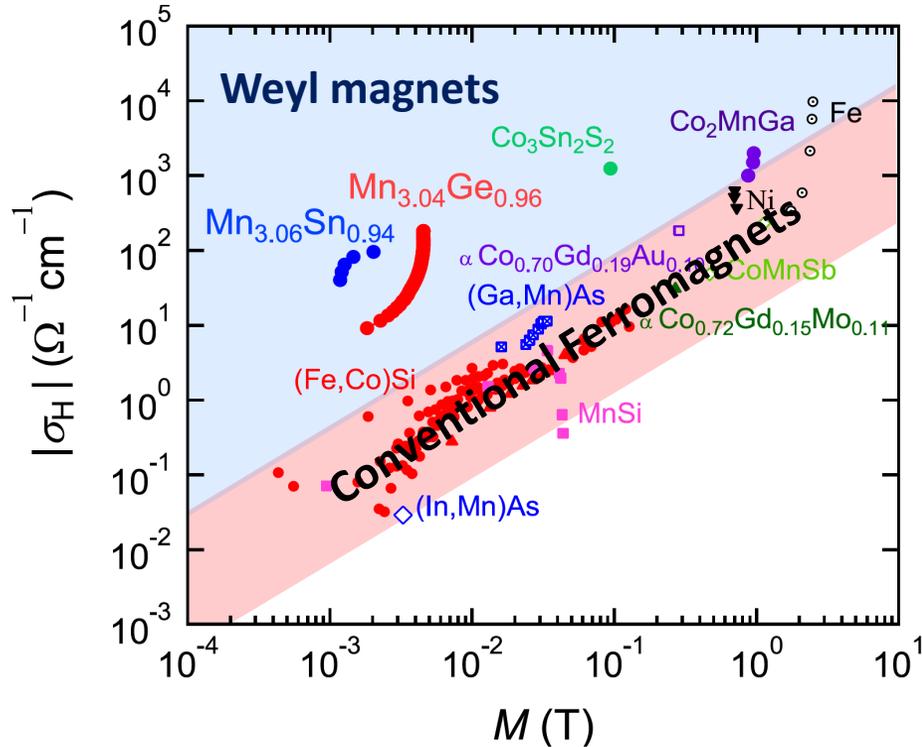
Strongly Anisotropic Magnetoconductance
Only when $E//B$, Positive Magnetoconductance

Magnetic Weyl Semimetals

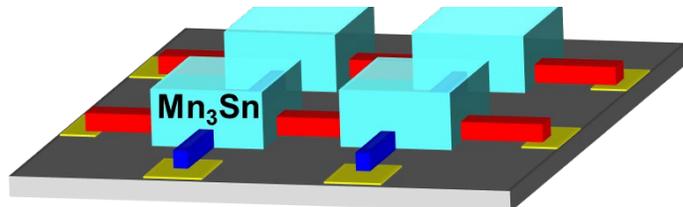


Weyl Magnets: Functional Magnets

Anomalous Hall Effect

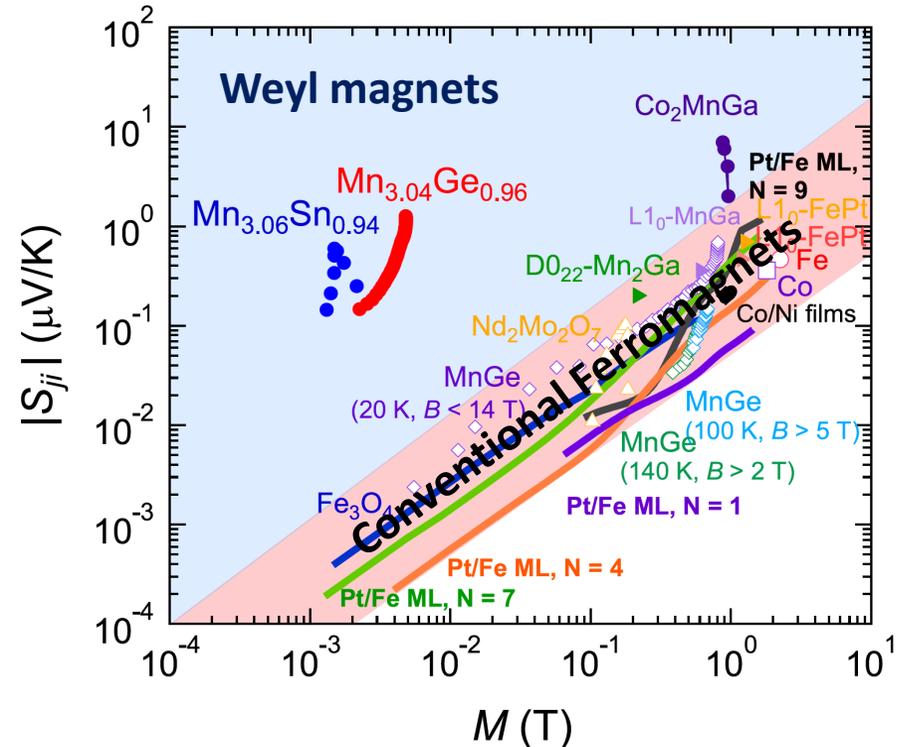


Non-volatile Memory

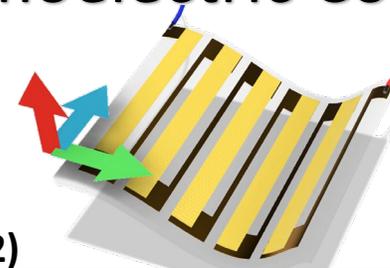


SN and R. Arita, *Annu. Rev. of Condens. Matter Phys.*, 13:119–42 (2022)

Anomalous Nernst Effect



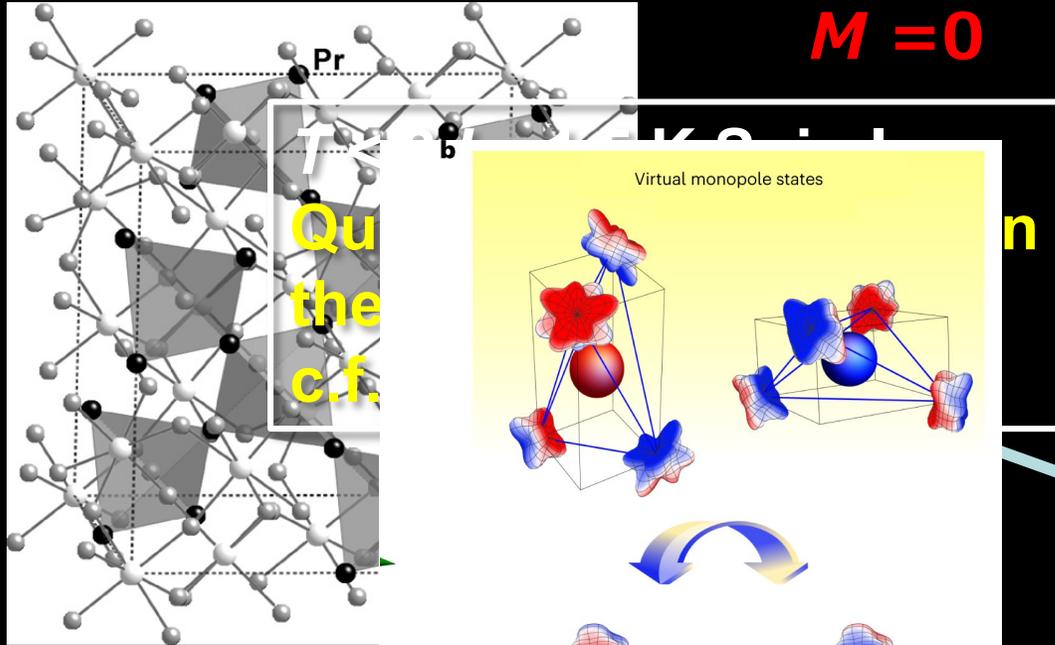
Thermoelectric Conversion



Large responses are obtained irrespective of size of M .

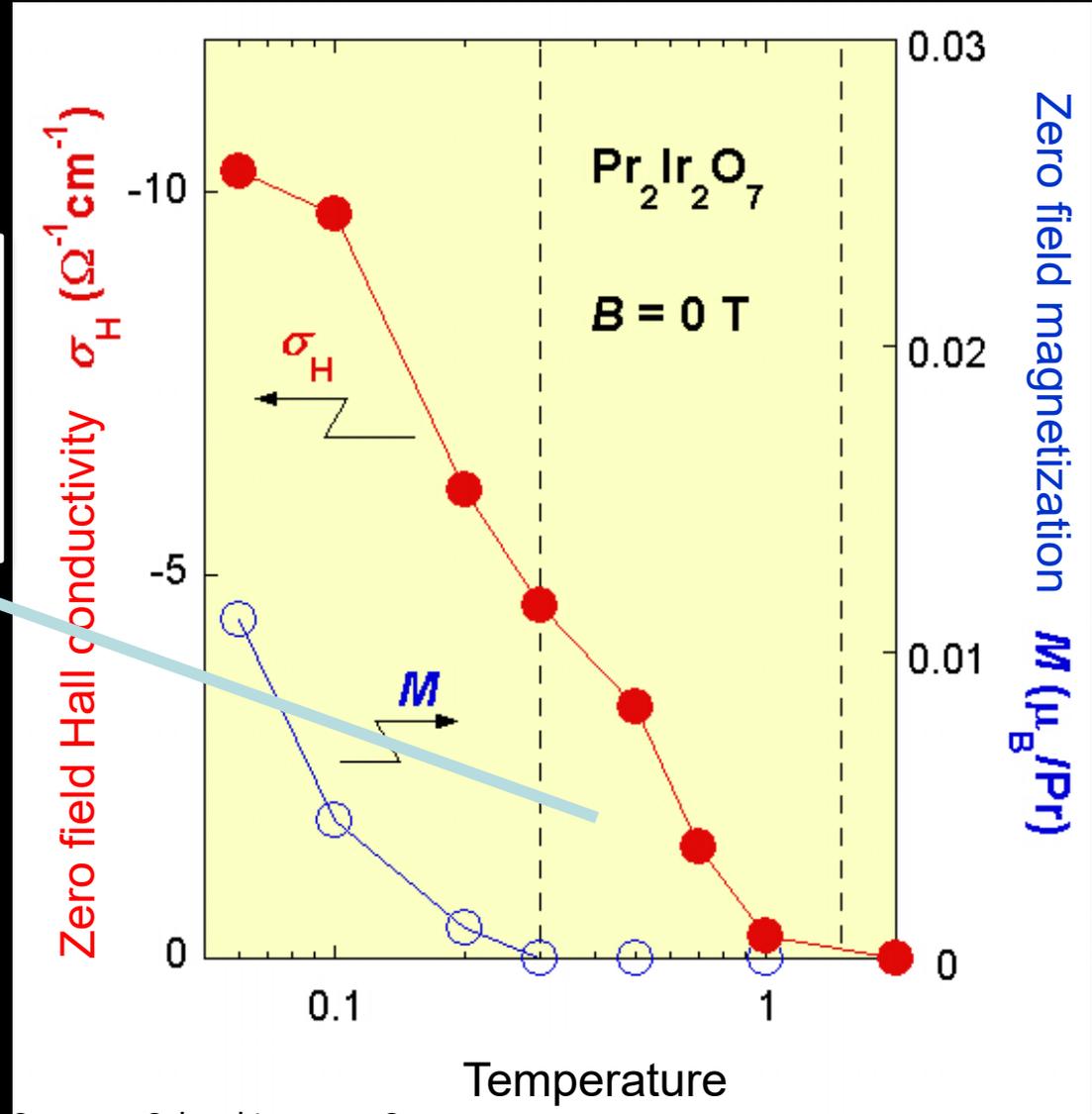
Spontaneous Hall Effect in Spin Liquid

Pr³⁺ 4f² non Kramers Ising moment **AHE w.**
 Ir⁴⁺ 5d⁵ conduction electron **B = 0**
M = 0



Quadrupolar moments (J_x & J_y) linearly couple to Strain → Dynamical Jahn-Teller Effect

Spin-Orbital Liquid State
 Tang et al., Nat. Phys. (2023)



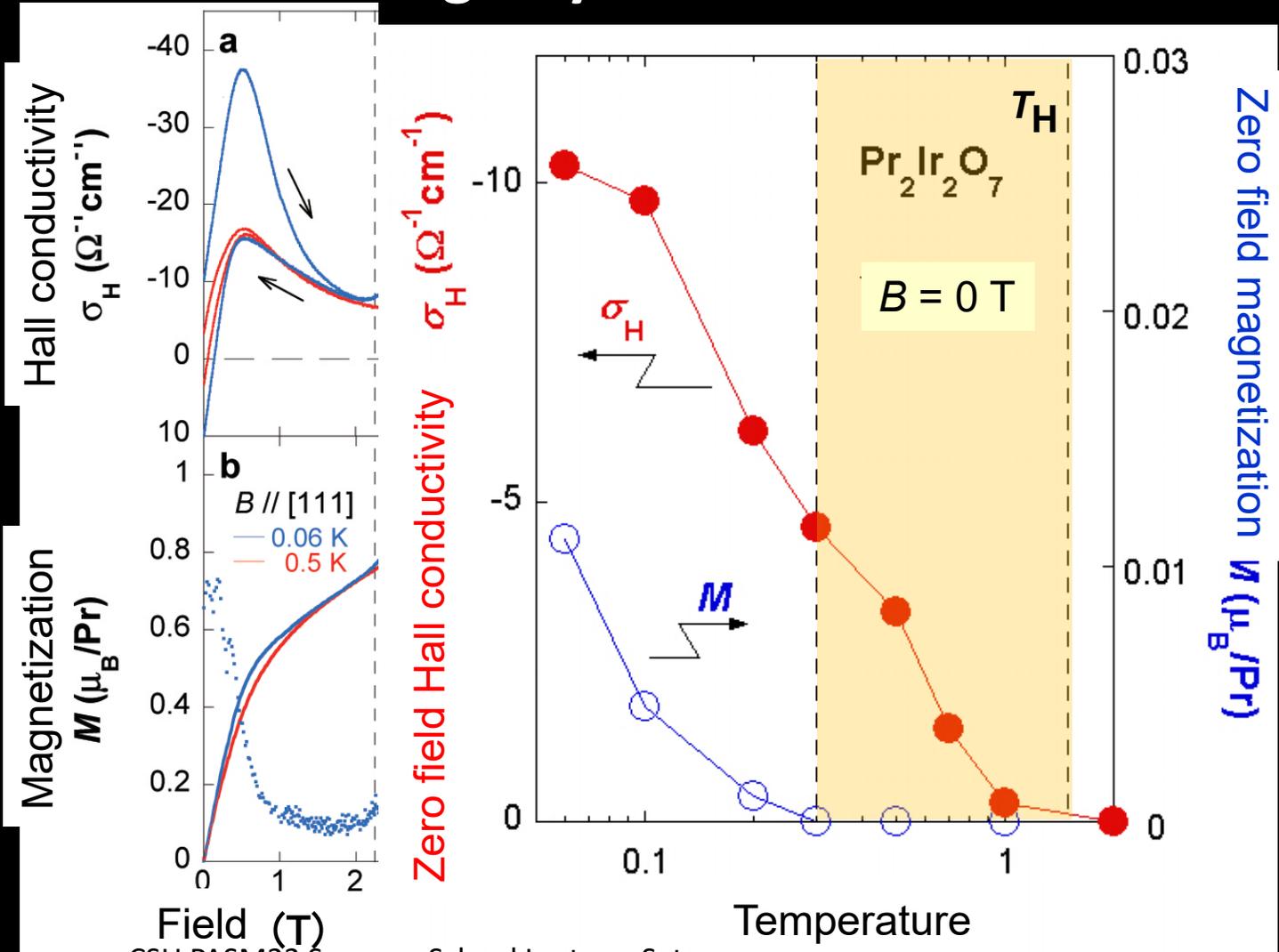
Machida et al., Nature (2009), Ohsuki et al., PNAS (2019). cf. Guo et al., PRB (2020).

Spontaneous Hall Effect in Spin Liquid

Large Berry Curvature in k -Space

Large Hysteresis in Hall Effect

No Hysteresis in Magnetization



Platform for correlated topological semimetals

PHYSICAL REVIEW B 83, 205101 (2011)



Topological semimetal and Fermi-arc surface states in the electronic structure of pyrochlore iridates

Xiangang Wan,¹ Ari M. Turner,² Ashvin Vishwanath,^{2,3} and Sergey Y. Savrasov^{1,4}

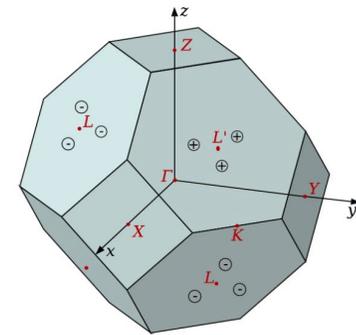
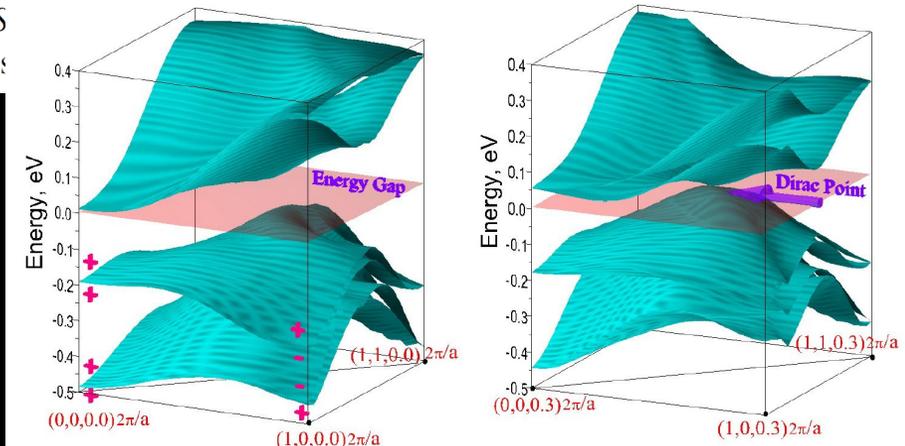
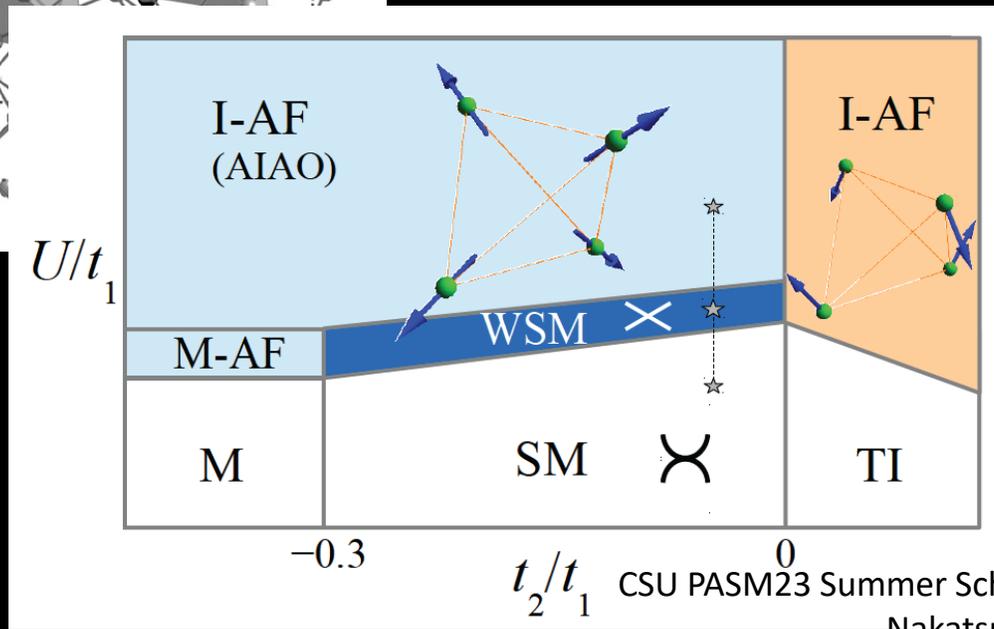
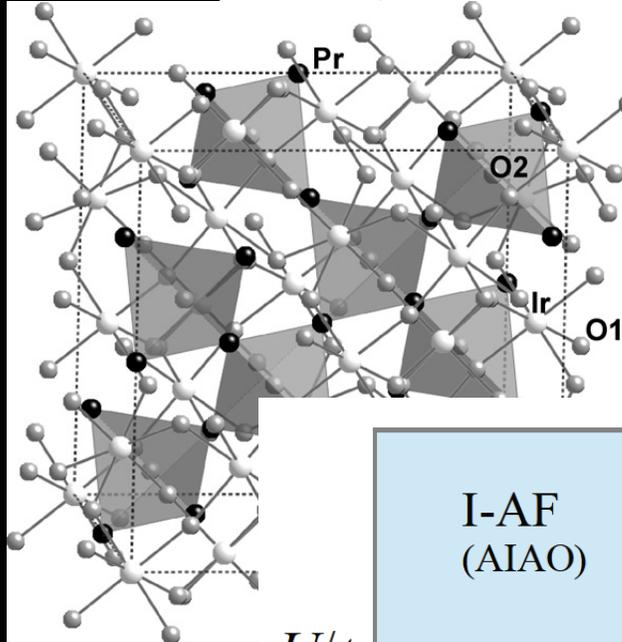
¹ *School of Solid State Microstructures and Department of Physics, Nanjing University, Nanjing 210093, China*

² *Department of Physics, University of California, Berkeley, California 94720, USA*

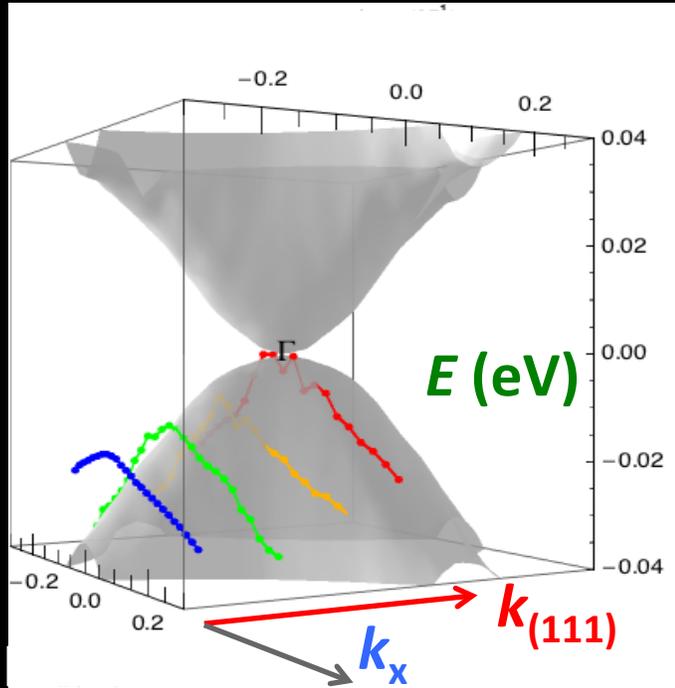
³ *Materials Sciences Division, Lawrence Berkeley National Laboratory, Berkeley, California 94720, USA*

⁴ *Department of Physics, University of California, Davis, One Shields Avenue, Davis, California 95616, USA*

(Received 23 February 2011; published 15 May 2011)



Quadratic band touching: Luttinger Semimetal



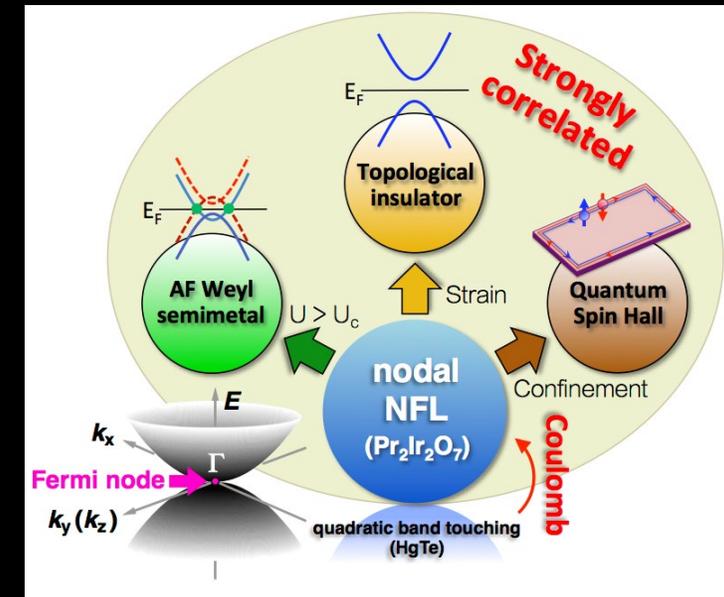
Exp. ARPES (UTokyo), THz (JHU+UTokyo)

Quadratic band touching at the Γ point

→ Luttinger Hamiltonian

$$H = \frac{k^2}{2M_0} + \frac{\left(\frac{5}{4k^2} - (k \cdot J)^2\right)}{2m} - \sum_{i=x,y,z} \frac{k_i^2 J_i^2}{2M_c}$$

- ❑ Non-Fermi liquid due to the strong interaction.
- ❑ Touching points are not topologically protected
- Parent states to various topological phases.
- ❑ Dielectric constant can be greatly enhanced.



J. M. Luttinger (1956)., A. A. Abrikosov and S. D. Beneslavskii (1971).

A. A. Abrikosov (1974)., S. Murakami *et al.* (2004)., E.-G . Moon *et al.* (2013). T. Kondo, SN *et al.* (2015).

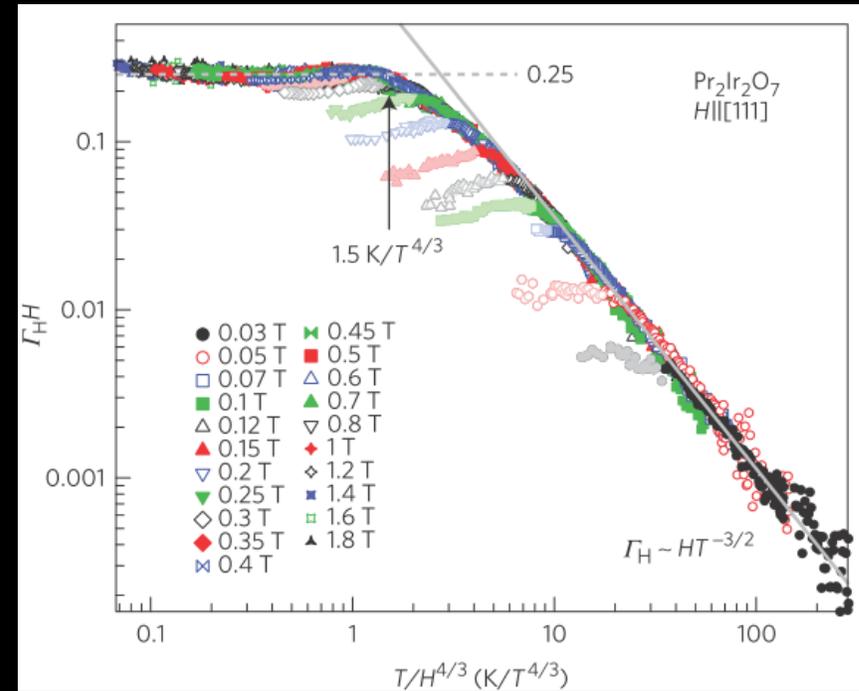
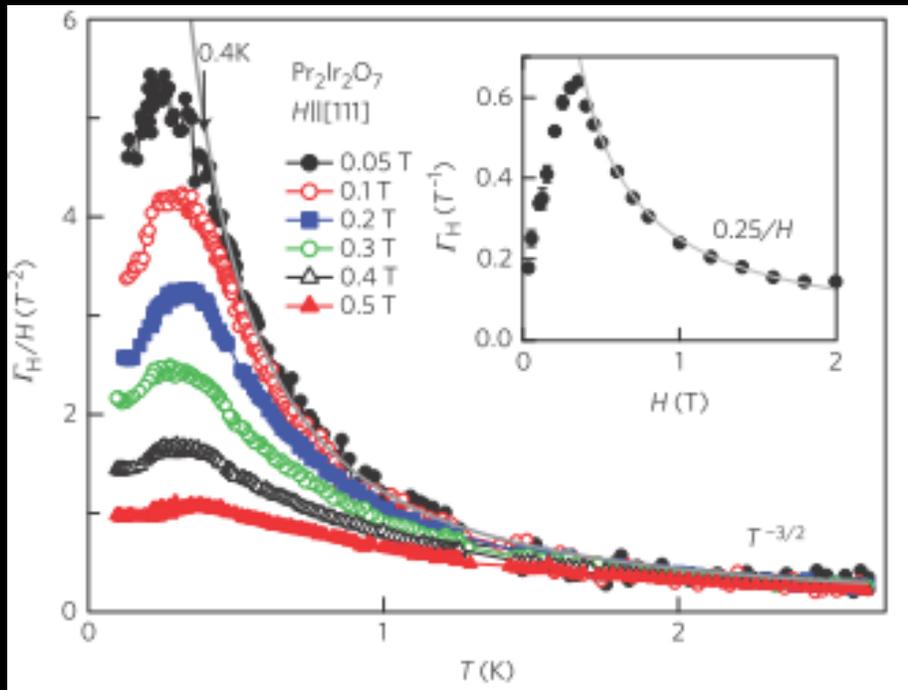
Zero field quantum criticality in $\text{Pr}_2\text{Ir}_2\text{O}_7$

Y. Tokiwa *et al.*, Nature Mat. **13**, 356 (2014).

Magnetic Grüneisen ratio \rightarrow divergence at field tuned QCP

$$\Gamma_H = -\frac{(\partial M/\partial T)_H}{C} = -\frac{1}{T} \frac{(\partial S/\partial H)_T}{(\partial S/\partial T)_H} = \frac{1}{T} \left(\frac{\partial T}{\partial H} \right)_S = \text{magnetocaloric effect}$$

[8] M. Garst *et al.*, PRB **72**, 205129 (2005). [9] L Zhu *et al.*, PRL **91**, 066404 (2003).



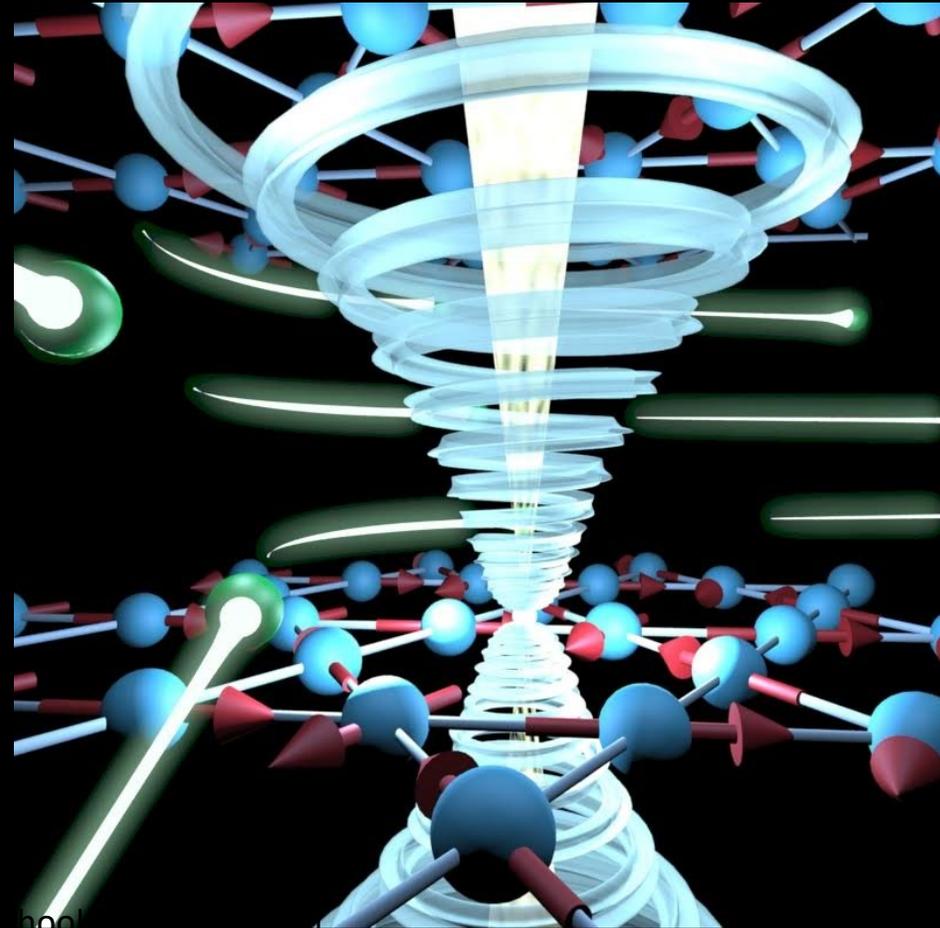
- Diverging Γ_H @ $H \rightarrow 0$ down to 0.4 K as $\Gamma_H \propto HT^{-3/2}$
- Scaling behavior in $T/H^{4/3}$ without critical field. \rightarrow zero field quantum critical point

Correlated topological semimetal

Various topological phases in correlated matter:
key observations: spontaneous Hall effect

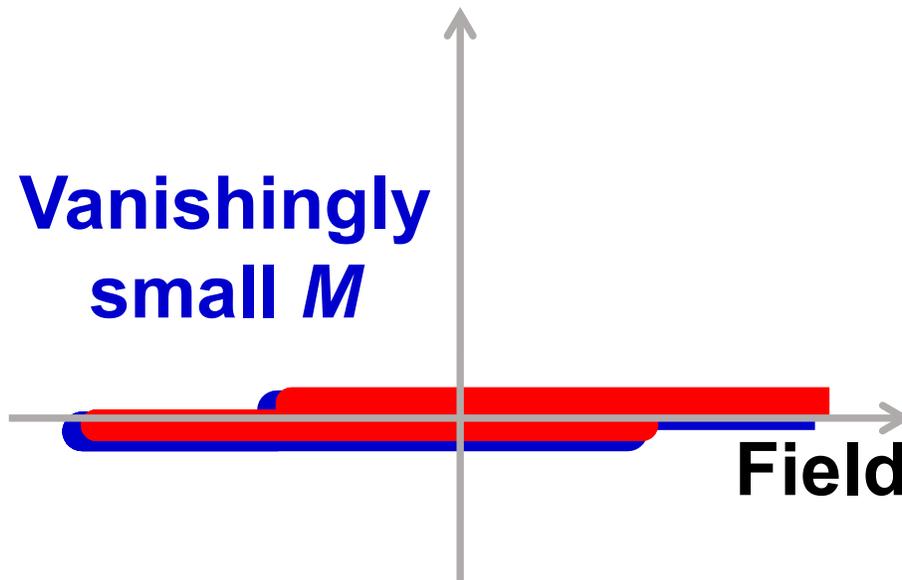
- Nonmagnetic/paramagnetic systems
 - Topological Non-Fermi Liquid: ex $\text{Pr}_2\text{Ir}_2\text{O}_7$
 - Weyl Kondo Semimetal: ex $\text{Ce}_3\text{Bi}_4\text{Pd}_3$
- Magnetic Systems
 - Quantum Anomalous Hall Effect ex Mag. Doped TI
 - Ferromagnetic Weyl semimetals: ex Co_2MnGa ,
 $\text{Co}_3\text{Sn}_2\text{S}_2$
 - Antiferromagnetic Weyl semimetal: ex Mn_3Sn**

Topological Antiferromagnets for Spintronics

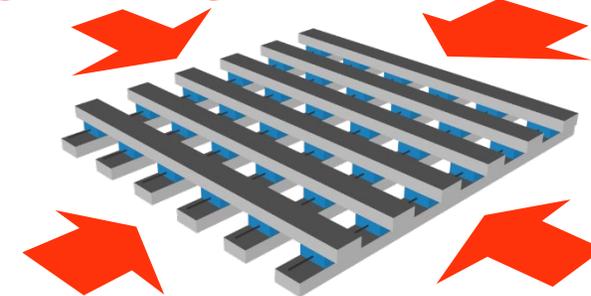


Antiferromagnetism: Spintronics

- *Produce no stray fields*
- *Robust against perturbation due to field*
- *Ultrafast dynamics (\sim THz)(cf. FM \sim GHz)*



High Integration Density



*High Speed
Data Processing*

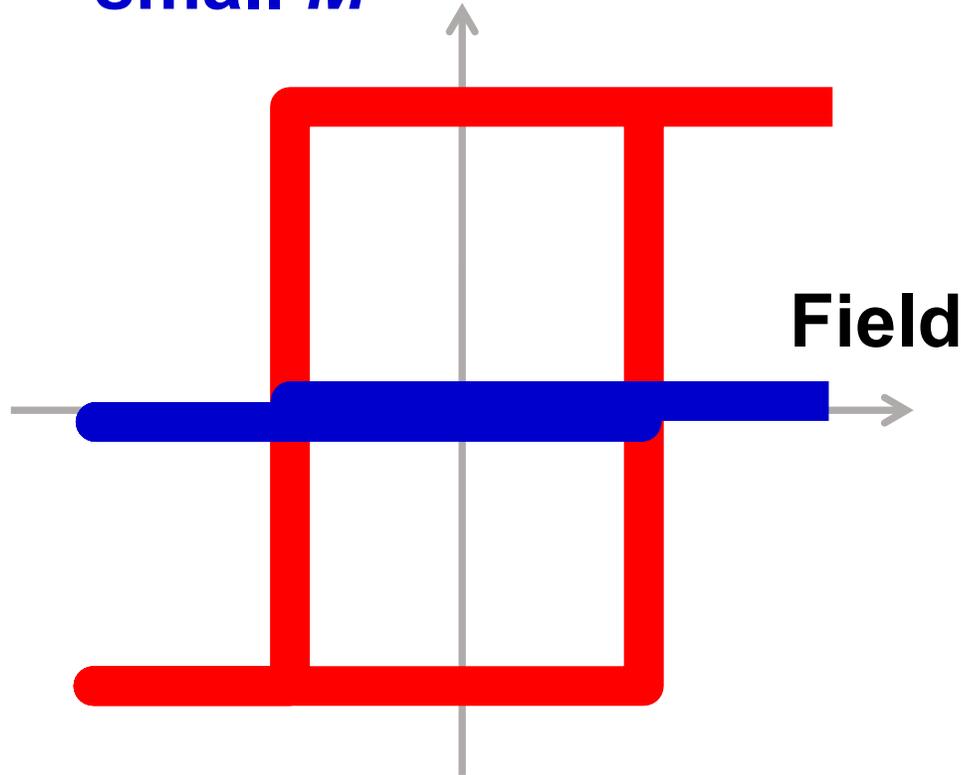
Hard to control, Small response



Topo. Functional Magnet Mn_3X

Large Response as in FMs

Vanishingly
small M



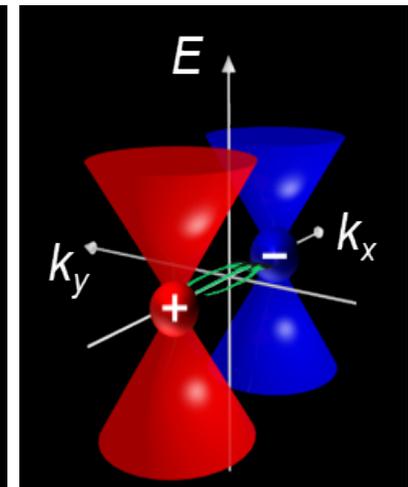
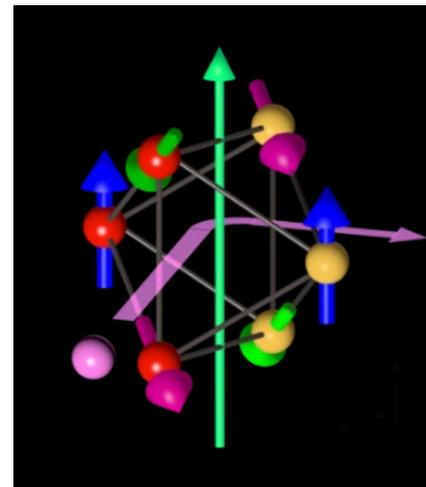
Dynamics \sim THz

Topological Weyl AFM

Mn_3Sn

Multipole

Weyl Points



Real Space

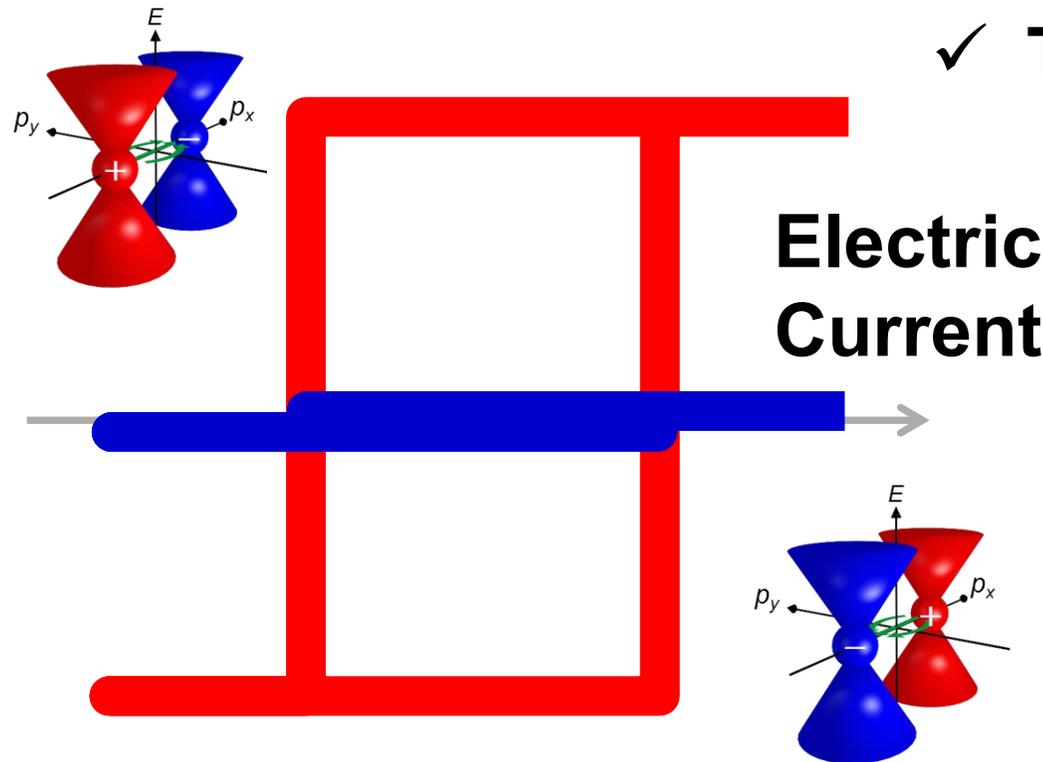
*Momentum
Space*

Electrical Manipulation

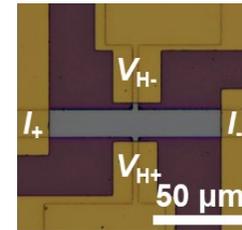
Tsai⁺, Higo⁺ et al., Nature 580, 608 (2020).

- **Electrical Switching of a Weyl Semimetallic State**

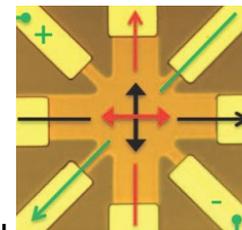
- ✓ Antiferromagnets
- ✓ The same protocols as in FMs



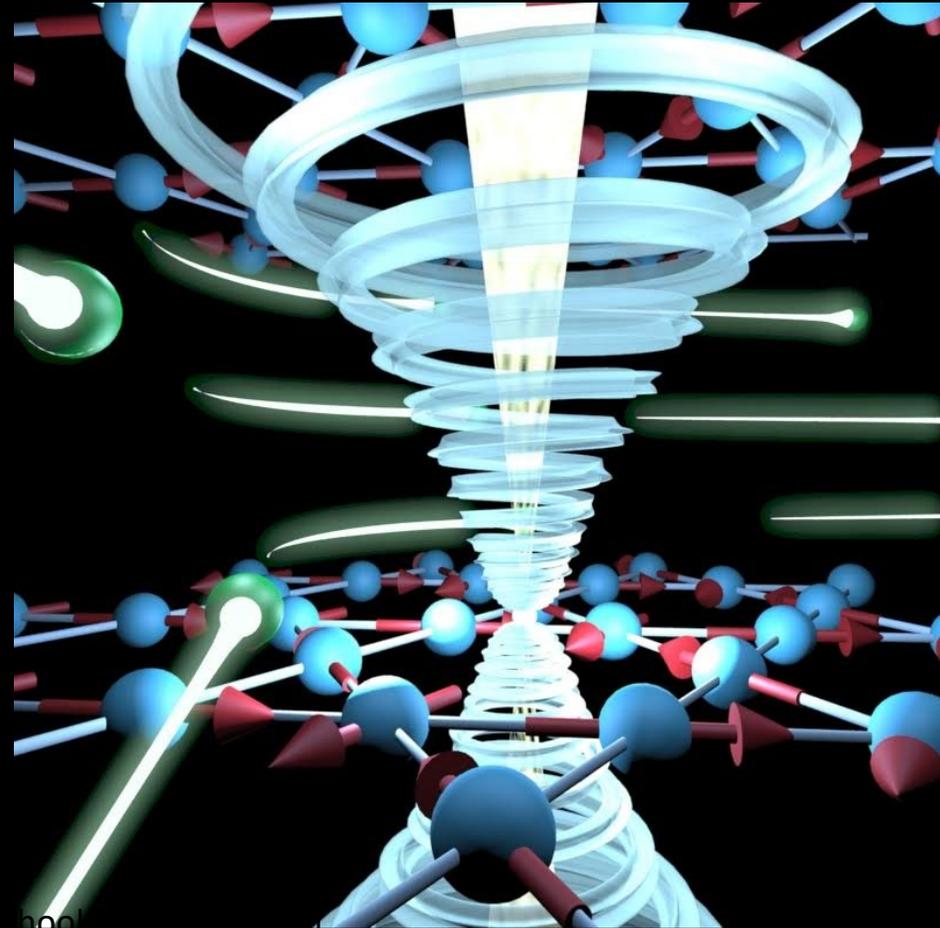
- Hall bar devices in AF Weyl SM



⇔ 8-term. for collinear AFMs

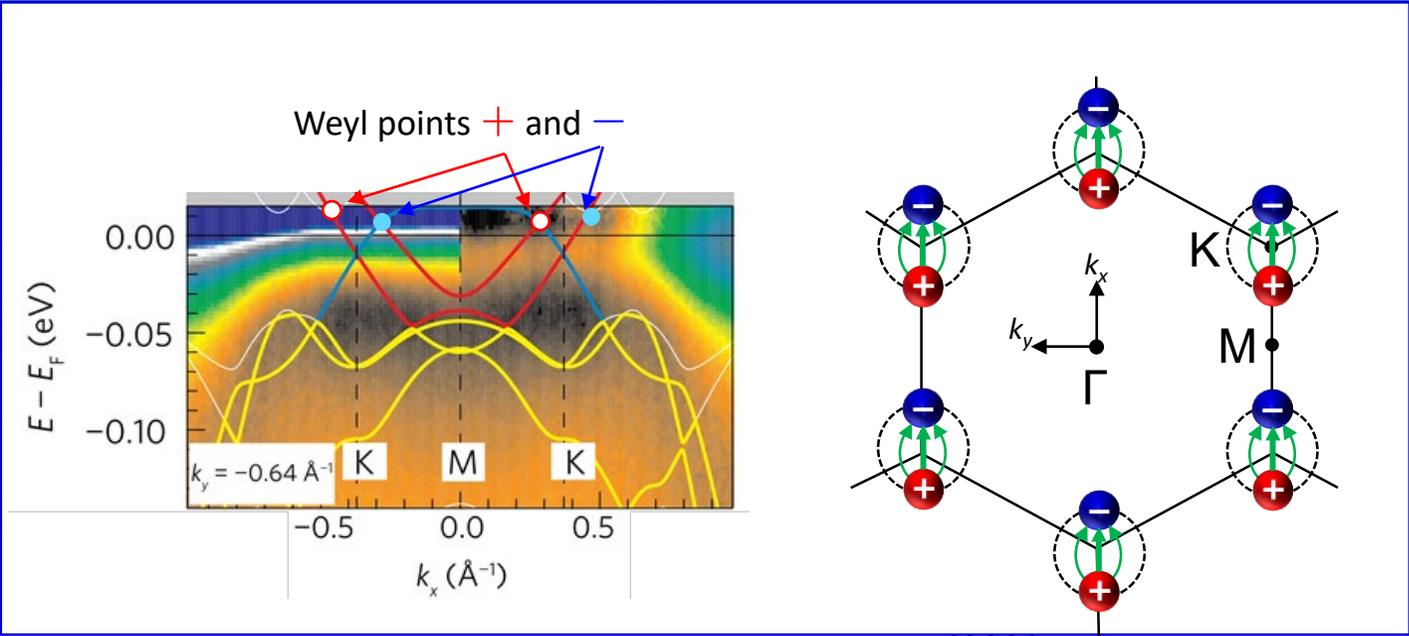
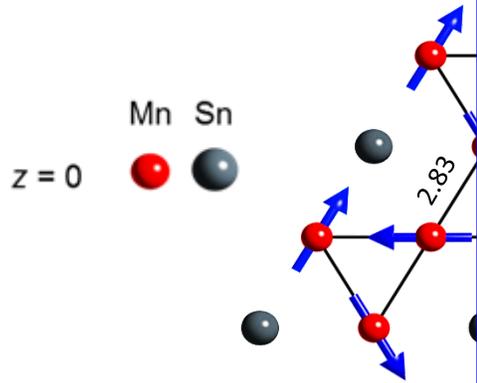


Weyl Semimetallic State in Mn_3Sn



Kagome Weyl AFM Mn_3X ($X = Sn, Ge$)

Chiral antiferromagn
@ $T_N = 430$ K

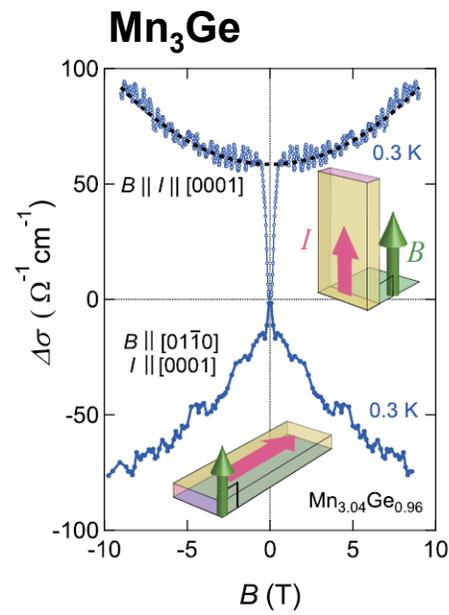
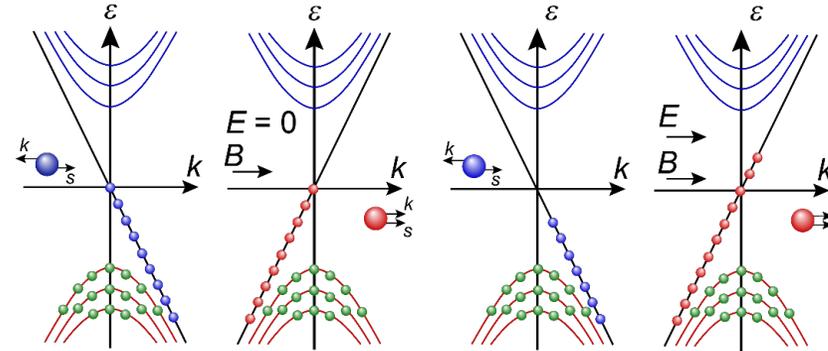
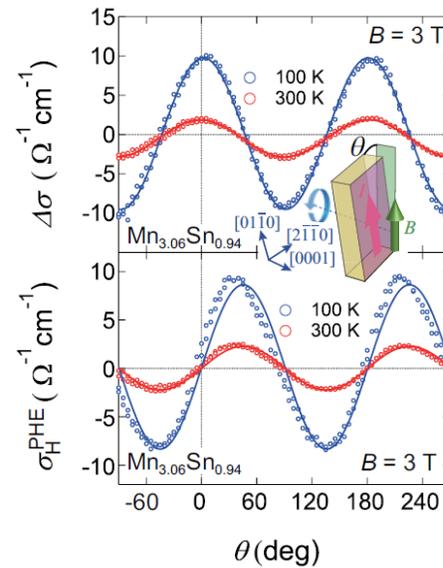
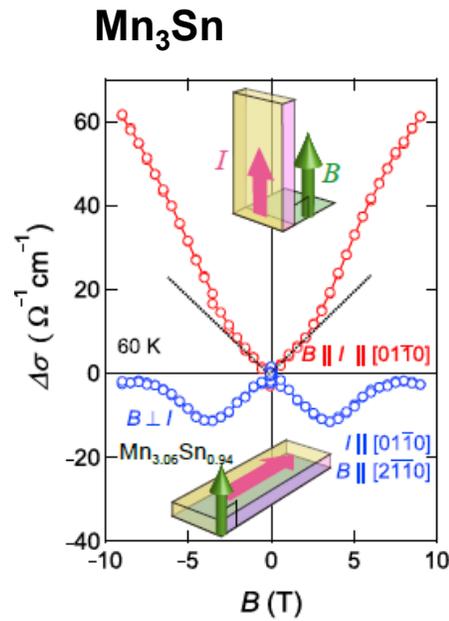


Despite the small spontaneous magnetic moment $\sim m\mu_B$,
large AHE is observed, comparable to the one in FM.

Weyl points close E_F w/ Strong correlation, Large Renormalization

S. N., N. Kiyohara, T. Higo, *Nature* (2015)., N. Kiyohara *et al.*, *Phys. Rev. Applied* (2016).
M. Ikhlas, T. Tomita, *et al.*, *Nature Physics* (2017).
K. Kuroda, T. Tomita, *et al.*, *Nature Materials* (2017)., T. Higo *et al.* *Nature Photon.* (2018).
Theory: Hua Chen *et al.* PRL (2014).

Chiral Anomaly in Antiferromagnets Mn₃Sn & Mn₃Ge



Chiral anomaly through the MC and PHE

Magnetoconductance $\Delta\sigma = \Delta\sigma_{\text{chiral}} \cos^2 \theta$

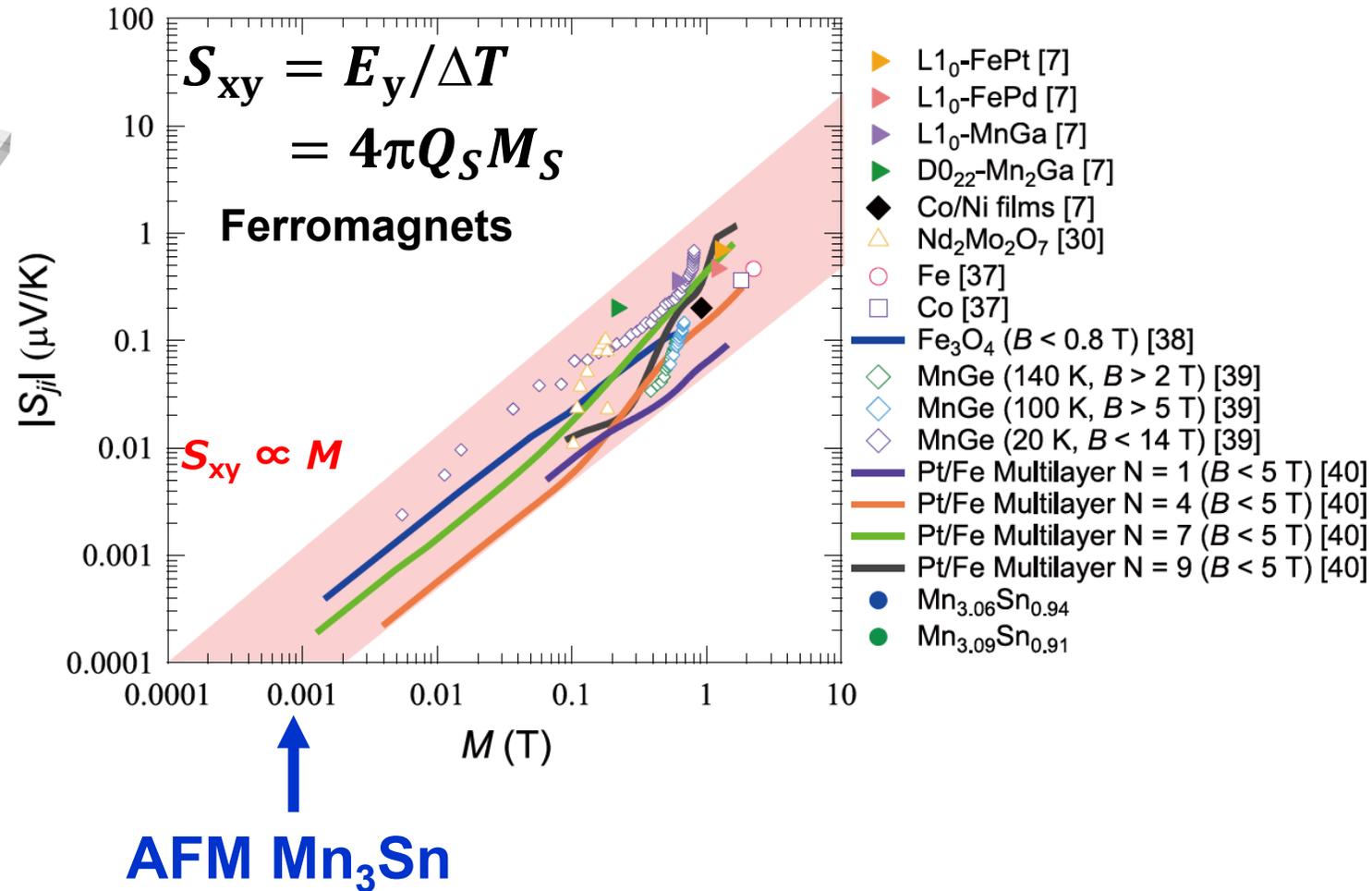
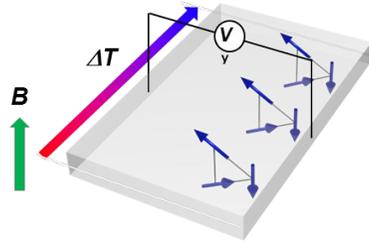
Planar Hall Effect $\Delta\sigma_H^{\text{PHE}} = \Delta\sigma_{\text{chiral}} \sin \theta \cos \theta$

Kuroda, Tomita, Kondo, SN *et al.*, *Nature Materials* (2017).

Chen, Tomita, Minami, Fu, SN *et al.*, *Nature Commun.* (2021).

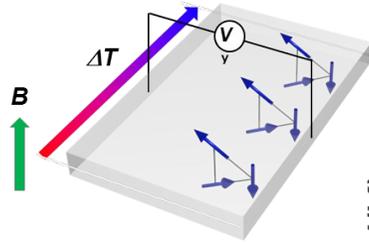
Nernst Effect vs. Magnetization

Nat. Phys. 2017



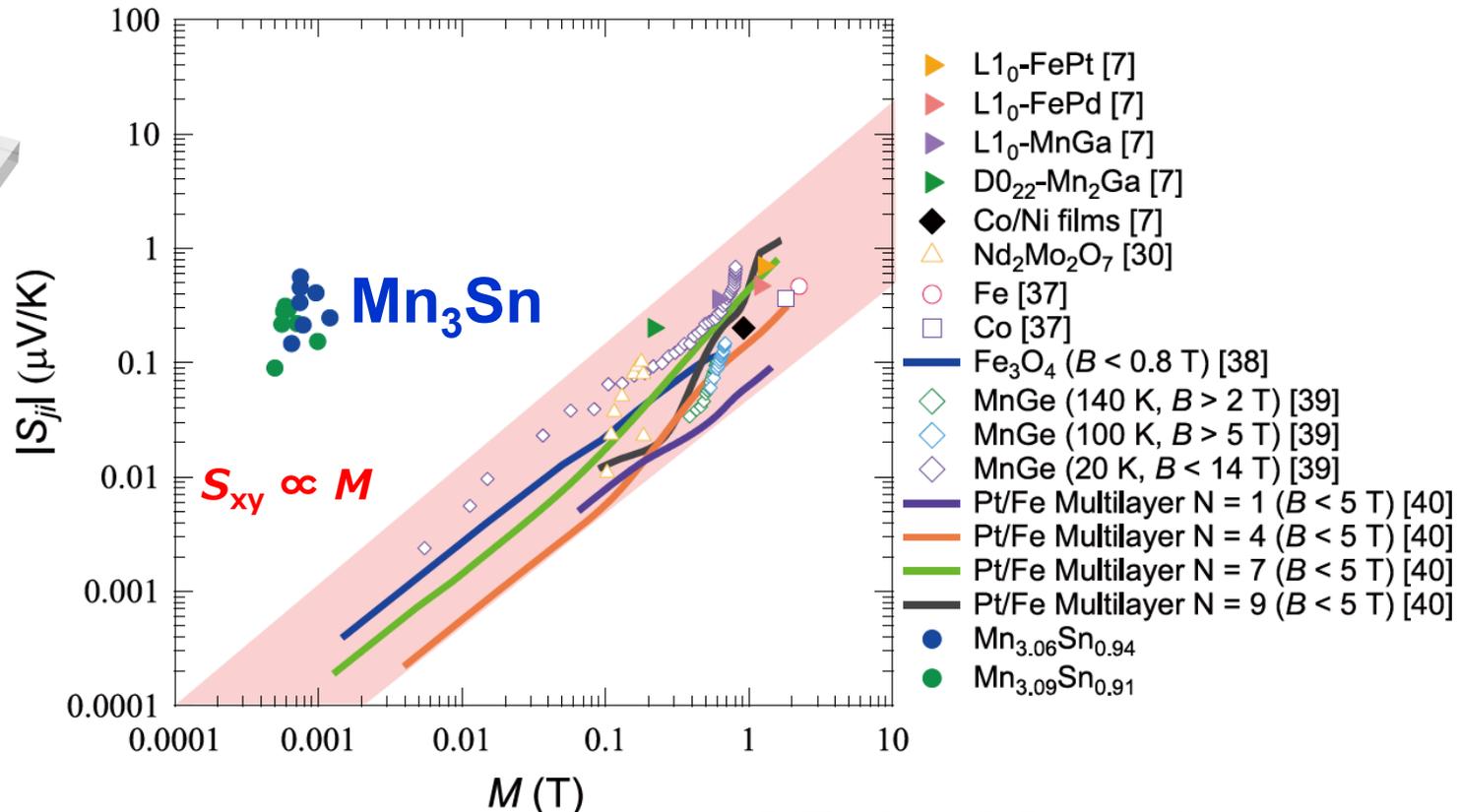
Nernst Effect vs. Magnetization

Nat. Phys. 2017



Ikhlas, Tomita et al.,
Nature Phys. (2017).

X. Li et al
PRL **119**, 056601
(2017).



Transverse Thermoelectric Conductivity $\alpha_{zx} = (S_{zx}/\rho_{zz}) + \sigma_{zx}S_{xx}$

$$\alpha_{zx} = -\frac{e}{T\hbar} \int \frac{dk}{(2\pi)^3} \Omega_{n,y}(k) \left\{ (\varepsilon_{nk} - \mu) f_{nk} + k_B T \ln [1 + e^{-\beta(\varepsilon_{nk} - \mu)}] \right\}$$

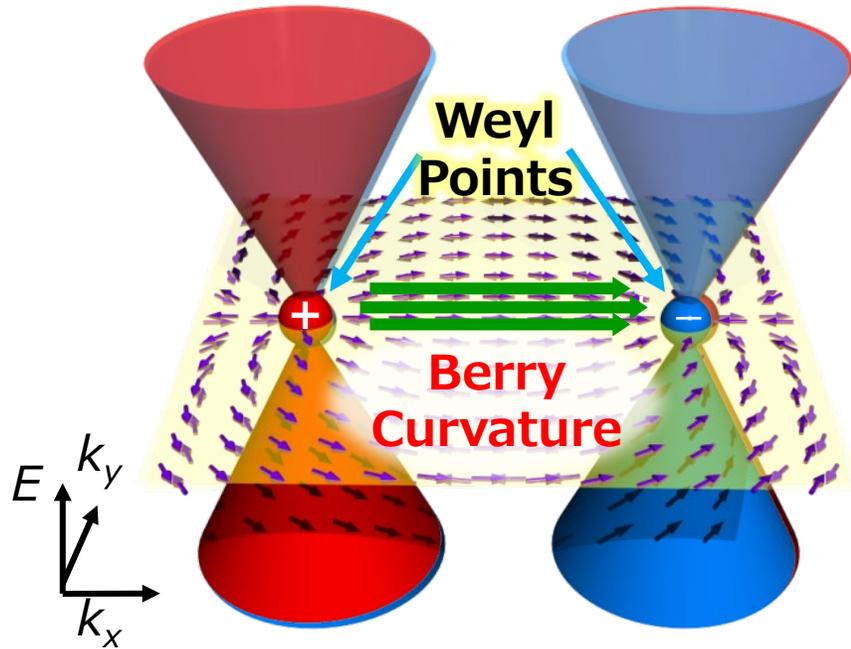
■ Nernst Effect : ~Berry curvature at Fermi Energy

100~1000 times more than ferromagnets

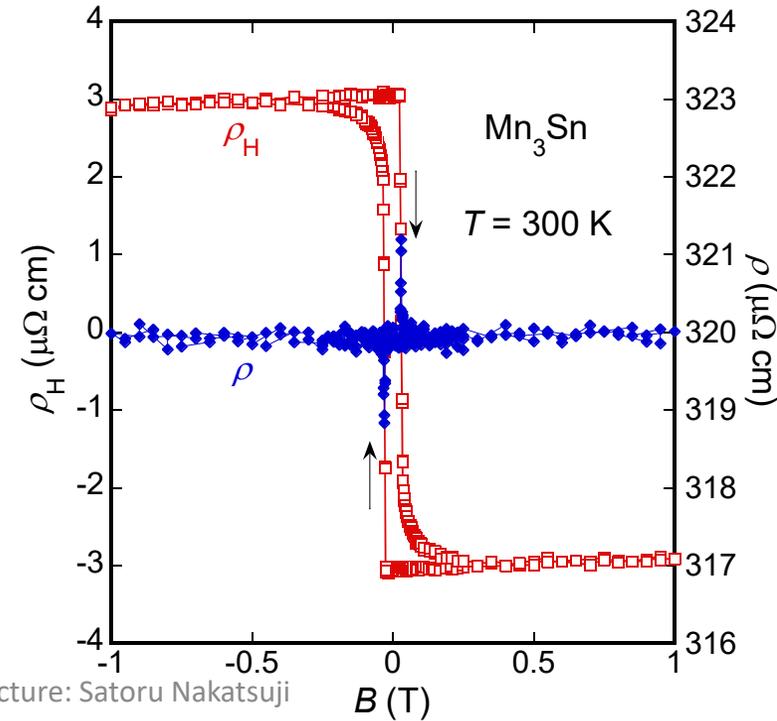
Large Berry Curvature near E_F

Mn₃Sn, Weyl Magnet

Control of Fictitious Field of a few 100 T by External Magnetic Field of 100 G.



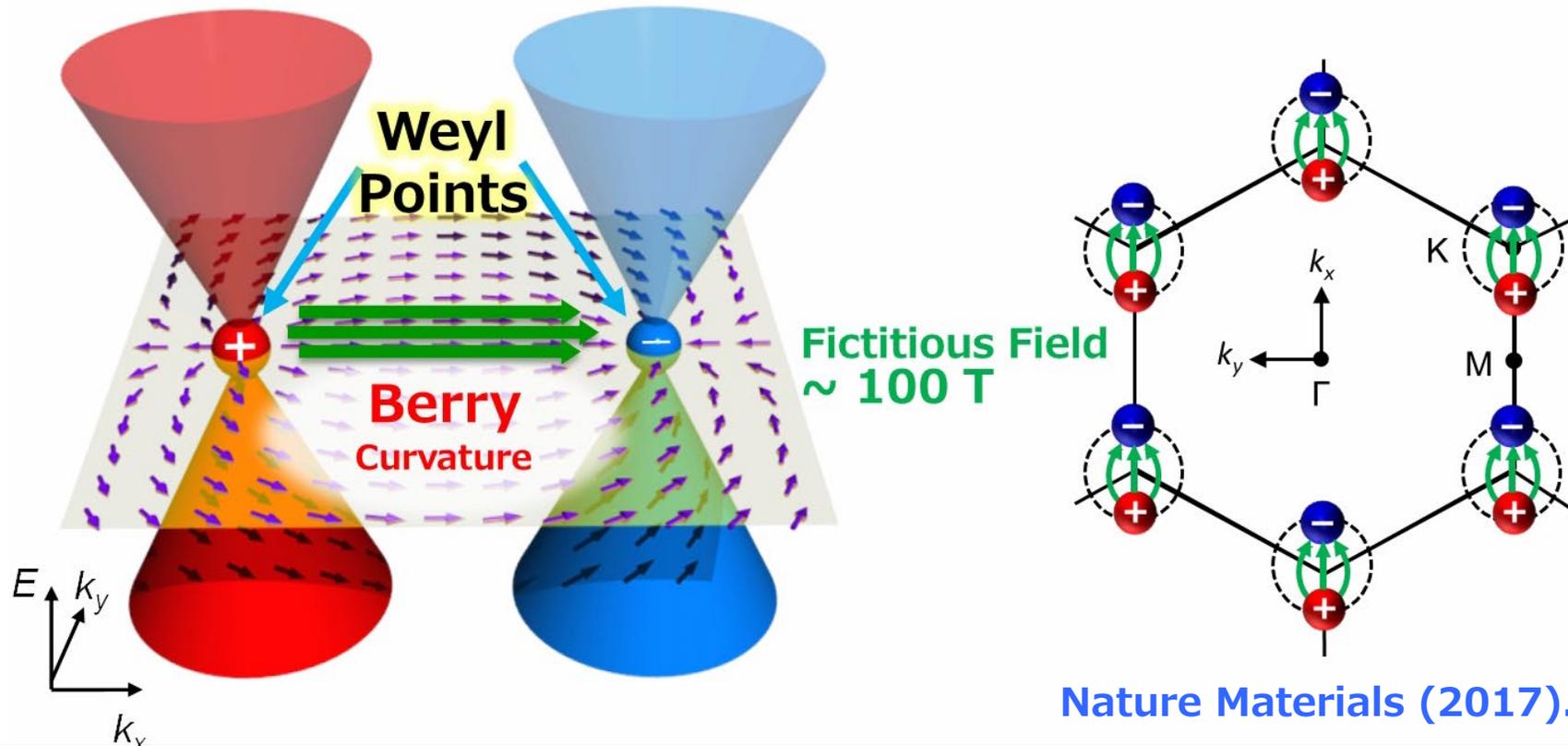
$$\sigma_{xy} = n \frac{e^2}{\hbar} \langle \Omega \rangle$$



Nature Materials (2017).

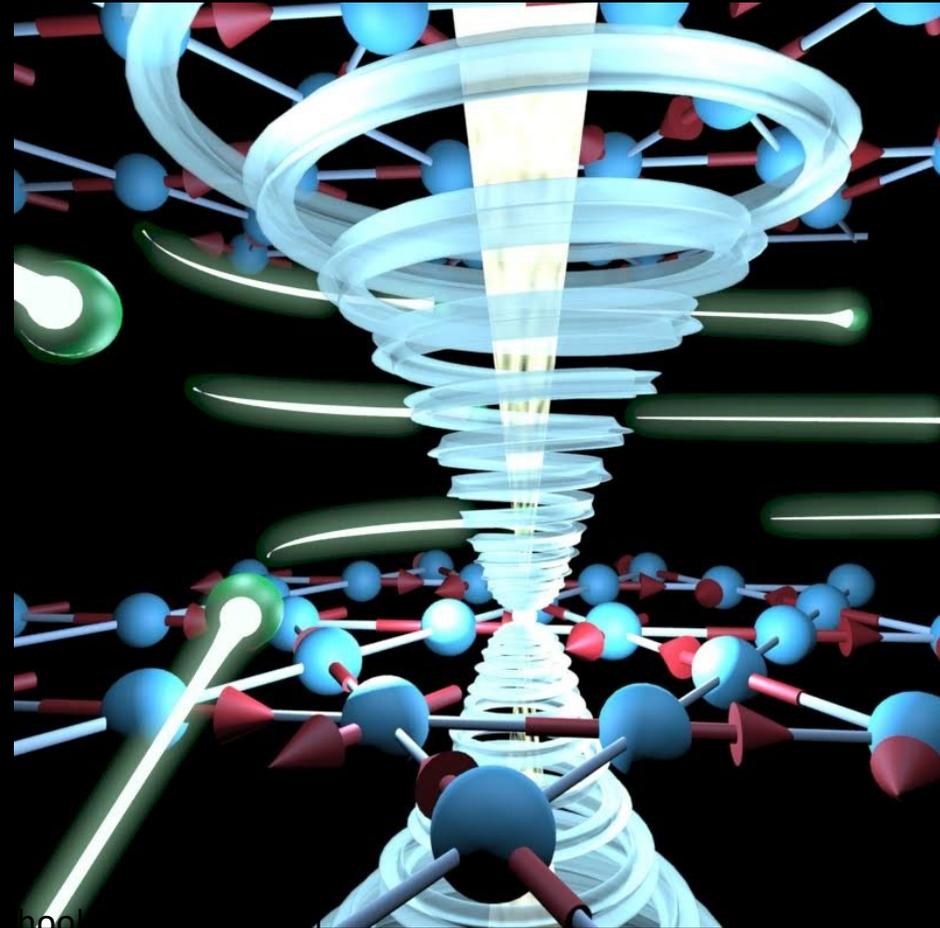
Control of Weyl Points

Control of Fictitious Field of a few 100 T by External Magnetic Field of 100 G.



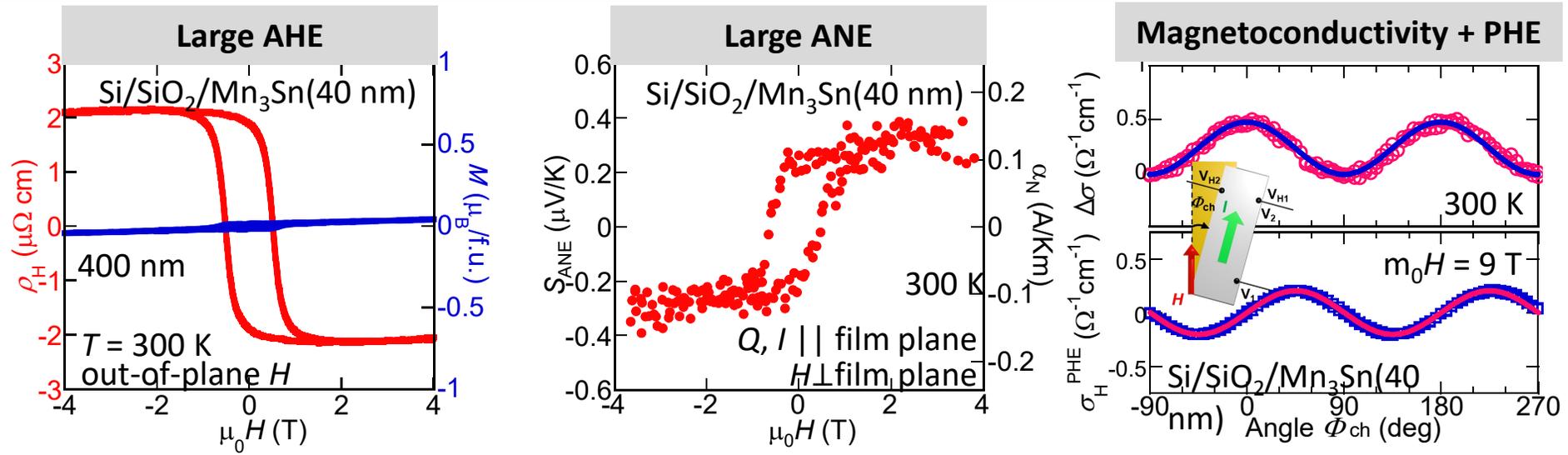
Manipulation of Weyl Points is useful for AF Spintronics

Electrical Manipulation of Weyl Semimetallic State in Mn_3Sn



Evidence for Weyl semimetal in Mn₃Sn films

Tsai⁺, Higo⁺ et al., Nature 580, 608 (2020).



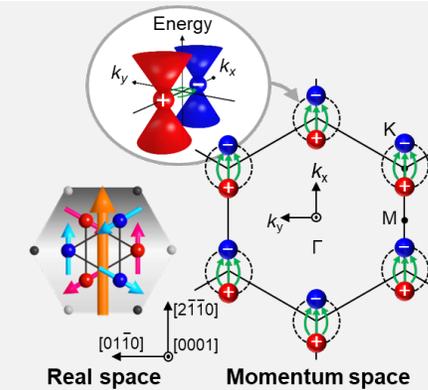
Higo et al., APL 113, 202402 (2018).

Tsai⁺, Higo⁺ et al., Nature 580, 608 (2020).

■ Evidence for the presence of Weyl fermion

1. ARPES **difficult for polycrystalline thin films**
2. Large ANE beyond the empirical law with M
100-1000 times larger ANE than that expected from M
3. Chiral anomaly through the MC and PHE

$$\text{MC} : \sigma = \sigma_{\perp} + \Delta\sigma_{\text{chiral}} \cos^2 \Phi_{\text{ch}} , \text{PHE} : \sigma_{\text{H}}^{\text{PHE}} = \Delta\sigma_{\text{chiral}} \sin \Phi_{\text{ch}} \cos \Phi_{\text{ch}}$$



Nandy et al., PRL 119, 176804 (2017).

Angular dependence of MC & PHE is well fitted by the equations

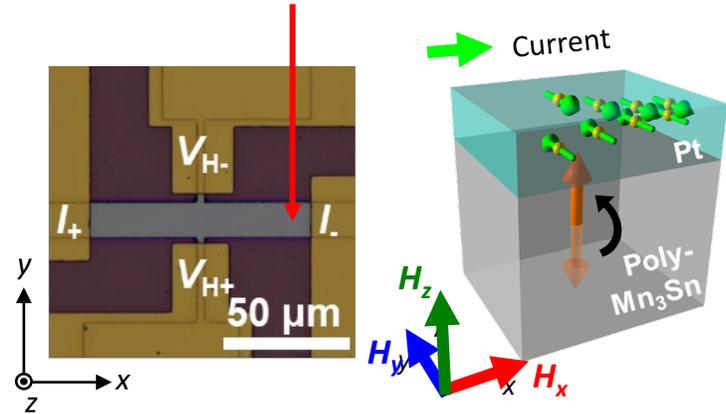
Similar to the bulk, Mn₃Sn films should have a Weyl semimetal state

Electrical Switching in Mn₃Sn/metal devices

Tsai⁺, Higo⁺ et al., Nature 580, 608 (2020).

Experimental setup

Si/SiO₂/Ru(2)/Mn₃Sn(40)/Pt or W or Cu/AlO_x(5)



Hall bar device

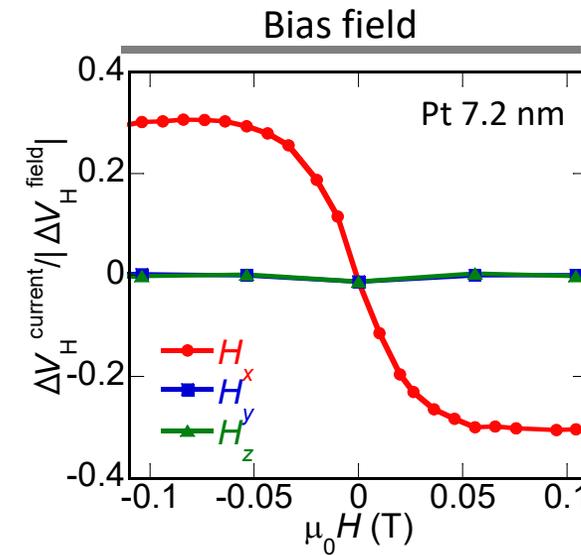
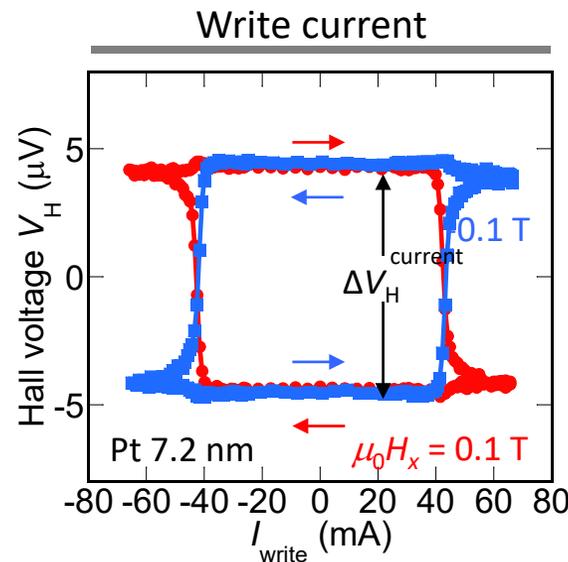
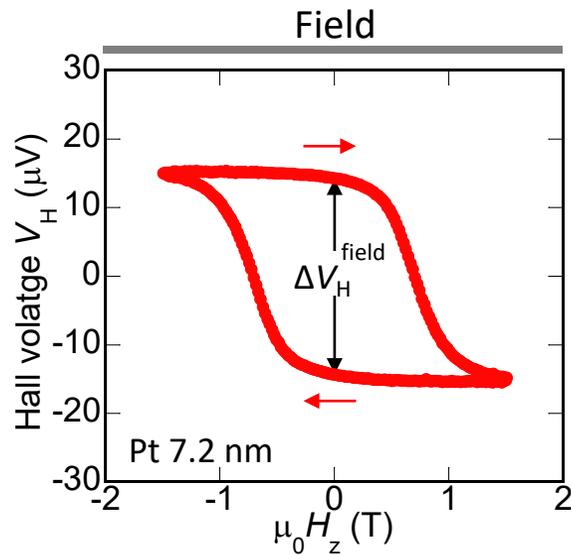
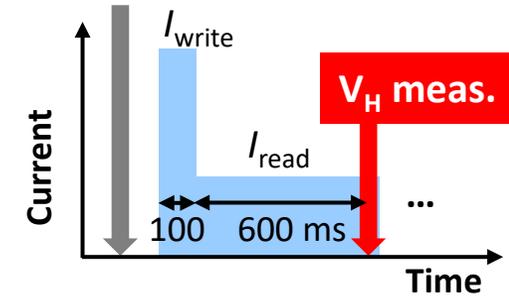
W/L=16 μm /96 μm

Read & Write Current

I (read) = 0.2 mA
 $|I$ (write)| < 80 mA
 @ R.T.



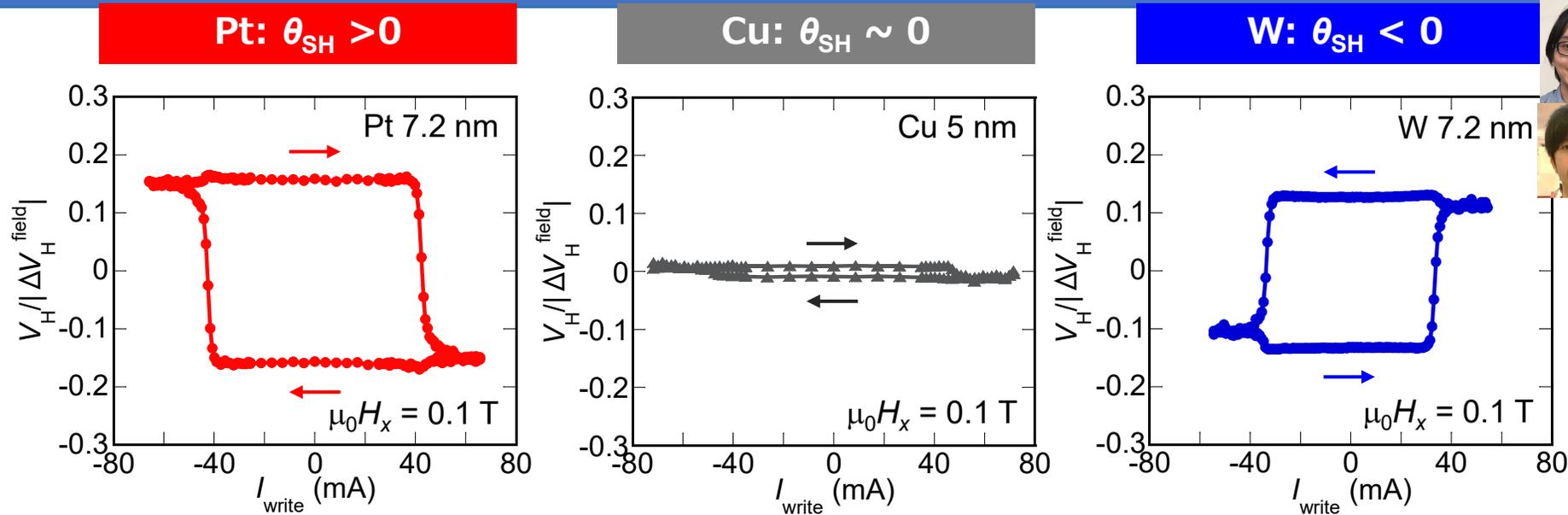
Magnetic field H



Symmetry consistent with SOT switching of the perpendicular M

SOT switching in Mn₃Sn/metal devices

Tsai⁺, Higo⁺ et al., Nature 580, 608 (2020).



■ The sign of the spin Hall angle θ_{SH} determines the sign of V_H

➡ **SOT from SHE in heavy metal (HM) layer** Oersted field

■ Critical current density : 2×10^{11} A/m² in Pt, 5×10^{10} A/m² in W

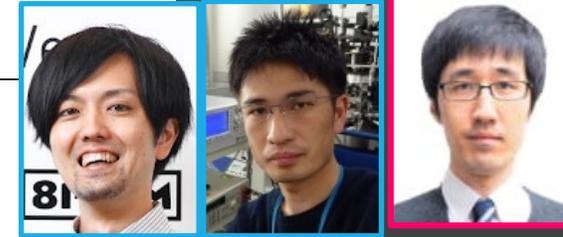
Comparable to other systems 【FM】 $\sim 10^{12}$ A/m², Miron *et al.*, Nature (2011); Liu *et al.*, Science (2012).

【AFM/FM】 10^{10} A/m², Fukami *et al.*, Nat. Mater. (2016).

【Collinear AFM】 10^{10} A/m², Wadley *et al.*, Science (2016).

The same switching protocol as that used for the FM/HM devices

Perpendicular full switching of chiral antiferromagnetic order by current



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Technology advancement

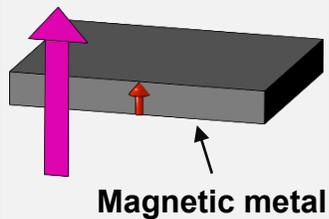
FM memory & sensor

Magnetic field

Spin-transfer torque (STT)

Spin-orbit torque (SOT)

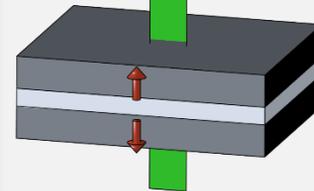
Magnetic field



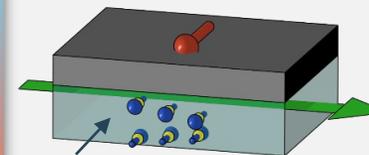
Magnetic metal

Magnetic field¹

Write current



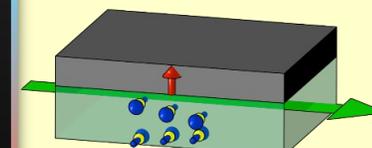
In-plane²



Heavy metal

Spin-orbit torque (SOT)

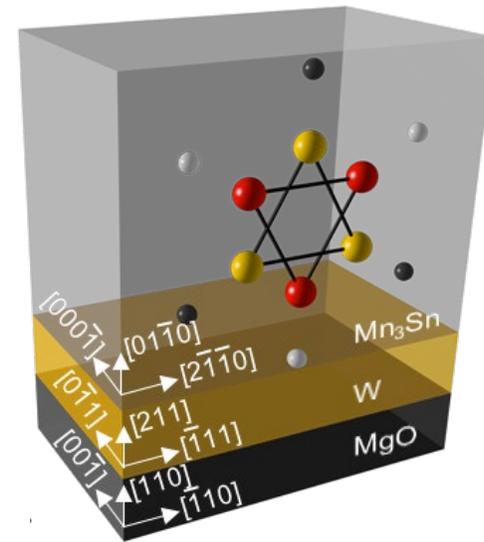
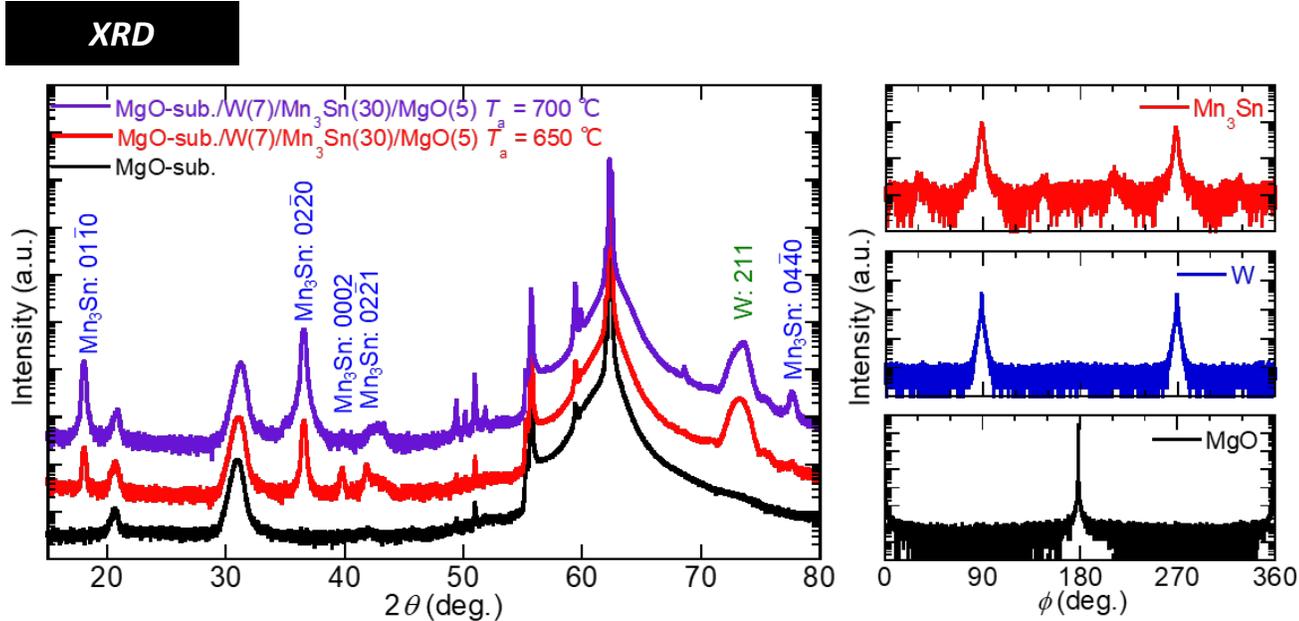
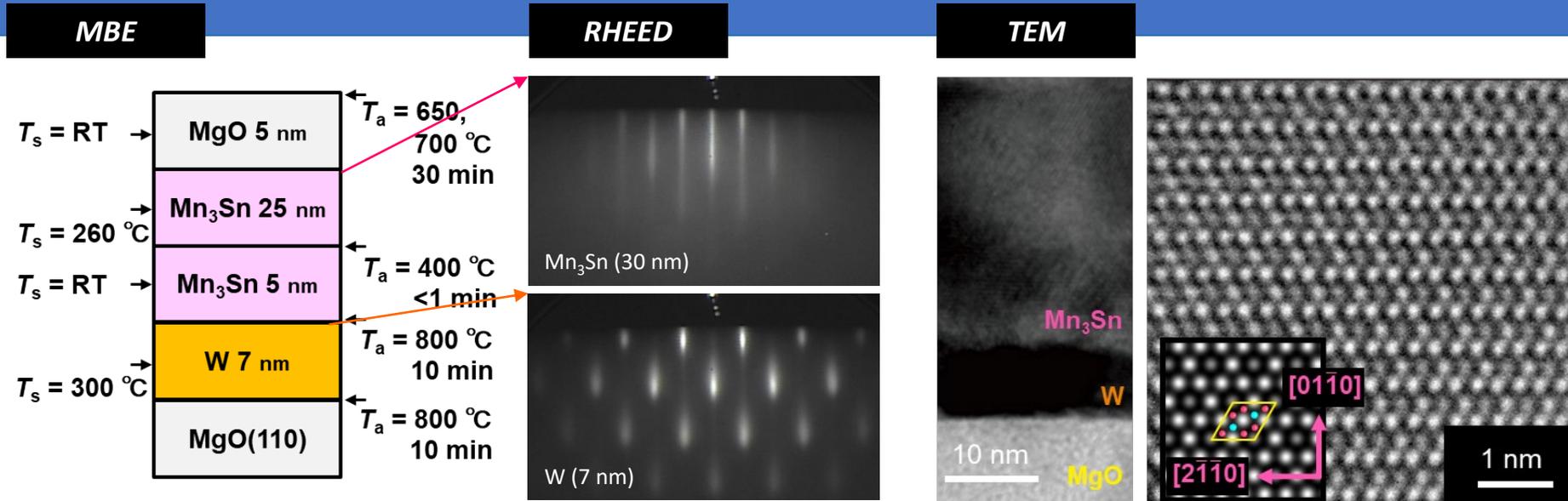
Perpendicular³



AFM memory & sensor

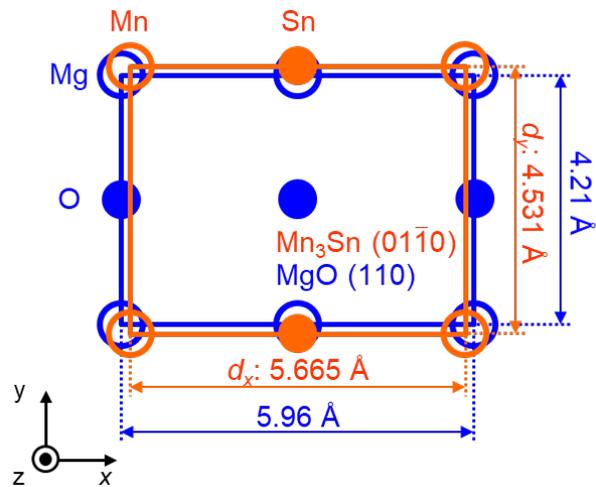
[1] S.N., Kiyohara, & Higo, Nature (2015). [2] Wadley et al., Science (2016), Moriyama et al., Sci. Rep. (2018), Chen et al., PRL (2018). [3] Tsai⁺, Higo⁺ et al., Nature (2020).

Mn₃Sn multilayer : fabrication & characterization

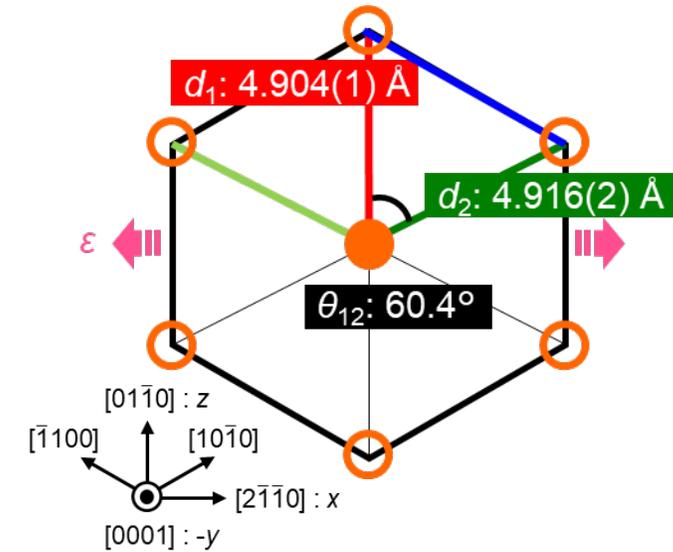
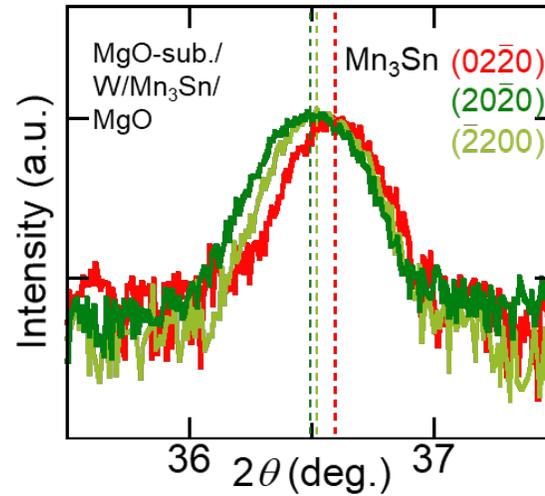


(01 $\bar{1}$ 0)-oriented epitaxial Mn₃Sn layer was obtained by MBE

Strained Epitaxial Mn₃Sn layer



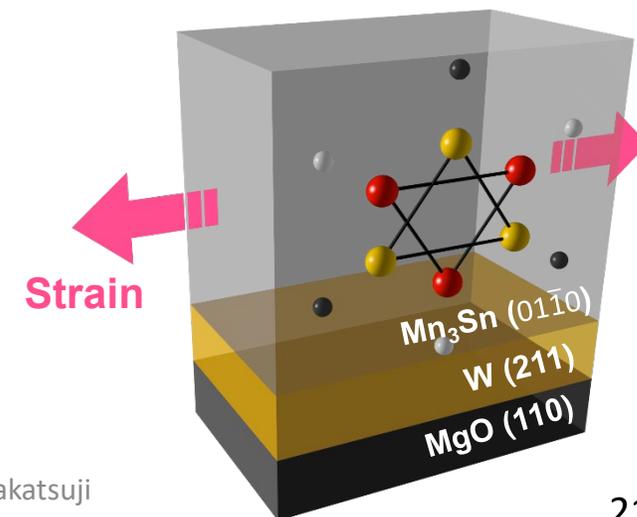
XRD



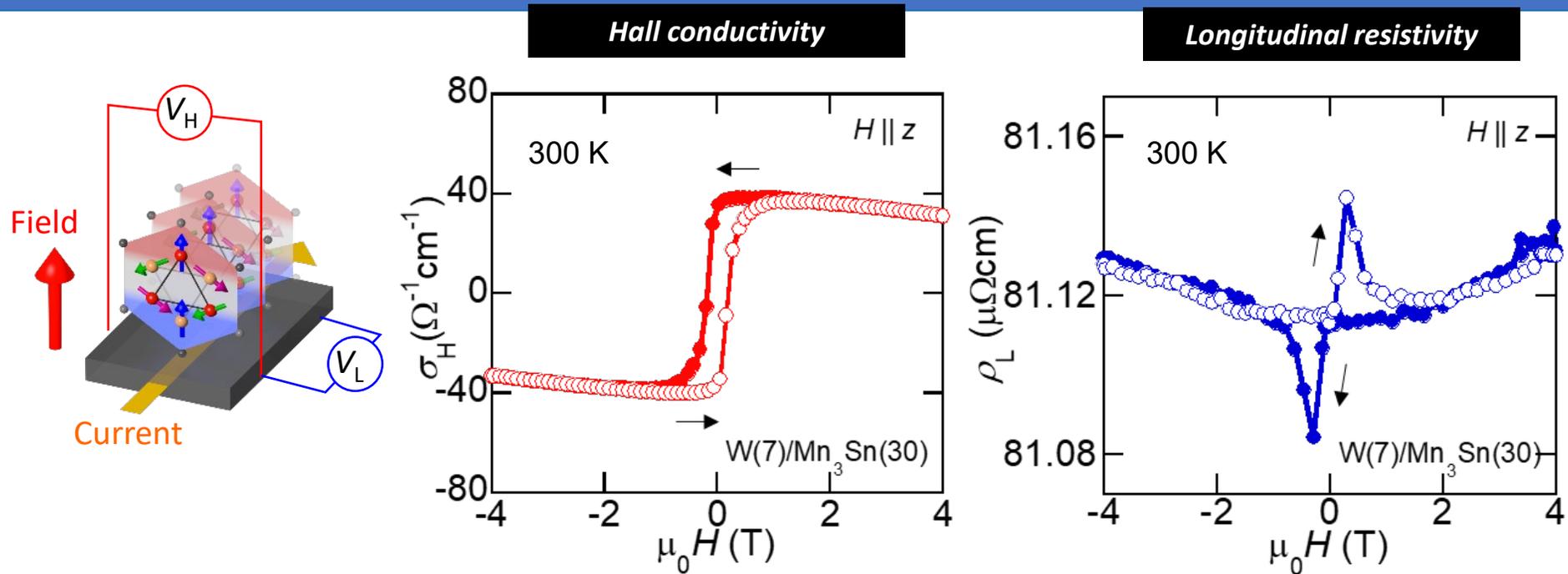
- In-plane tensile strain $\sim 0.2\%$ || [2 $\bar{1}$ $\bar{1}$ 0] in Mn₃Sn due to lattice mismatch between Mn₃Sn & MgO

Mn₃Sn : $d_x = 5.665$ Å & $d_y = 4.531$ Å in (01 $\bar{1}$ 0)

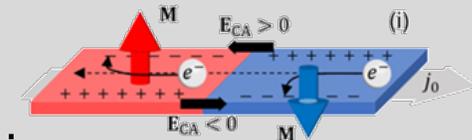
MgO : $d_x = 5.96$ Å & $d_y = 4.21$ Å in (110)



MBE-grown (W/)Mn₃Sn layer : transport properties



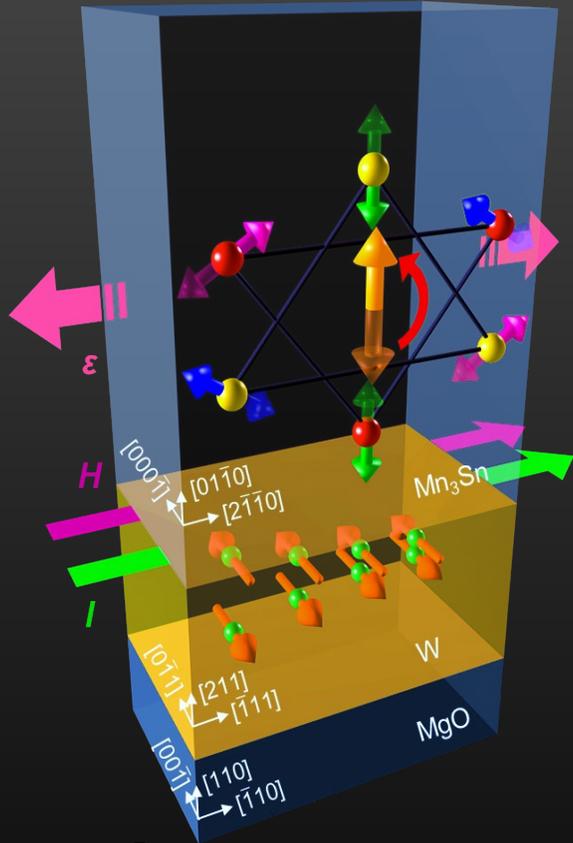
- Large AHE $\sigma_H \sim 40 \Omega^{-1}\text{cm}^{-1}$ (Bulk : 30-40 $\Omega^{-1}\text{cm}^{-1}$, Film : 20-30 $\Omega^{-1}\text{cm}^{-1}$)
- Small coercivity $\mu_0 H \sim 0.15 \text{ T}$ (Bulk : 0.05 T, Film : 0.6 T)
- Asymmetric magnetoresistance \Rightarrow large magnetic domain



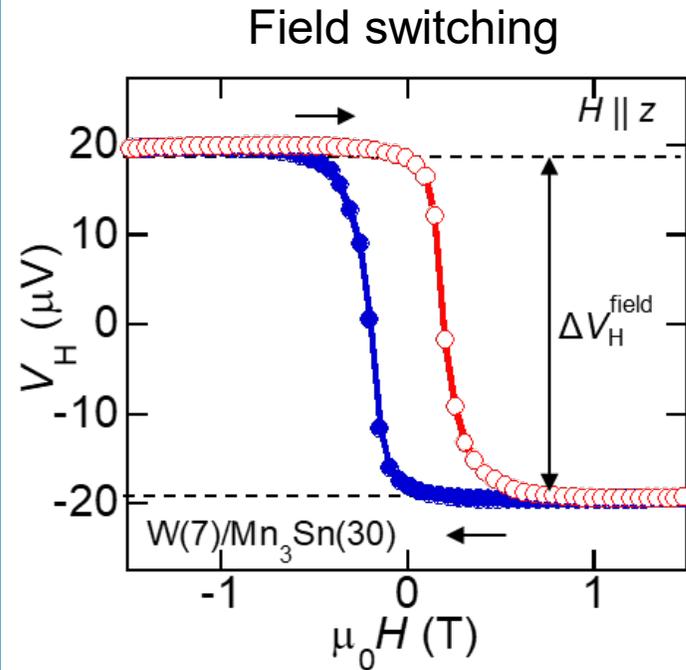
Sugimoto et al., Commun. Phys. 3, 111 (2020).

High crystallinity MBE-grown Mn₃Sn layer is achieved !

First demonstration of full electrical switching in an antiferromagnet

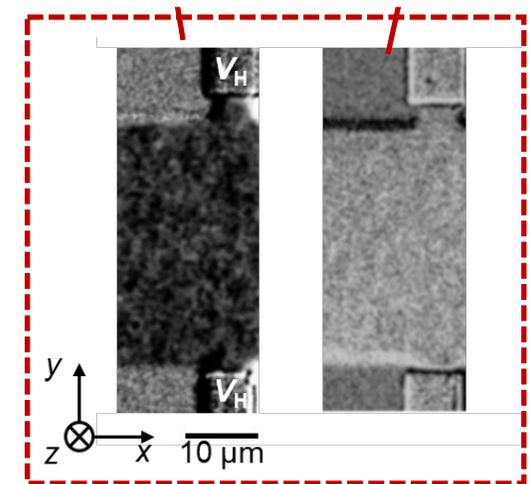


- Heavy metal (HM)/Mn₃Sn heterostructures fabricated by molecular beam epitaxy (MBE)
- Epitaxial in-plane tensile strain



The first demonstration of **100 %** electrical switching in an AFM material!
→ Crucial for **high-speed operation** and **dense integration**.

Higo[†], Kondou[†] *et al.*, Nature (2022).



full switching confirmed by polar MOKE

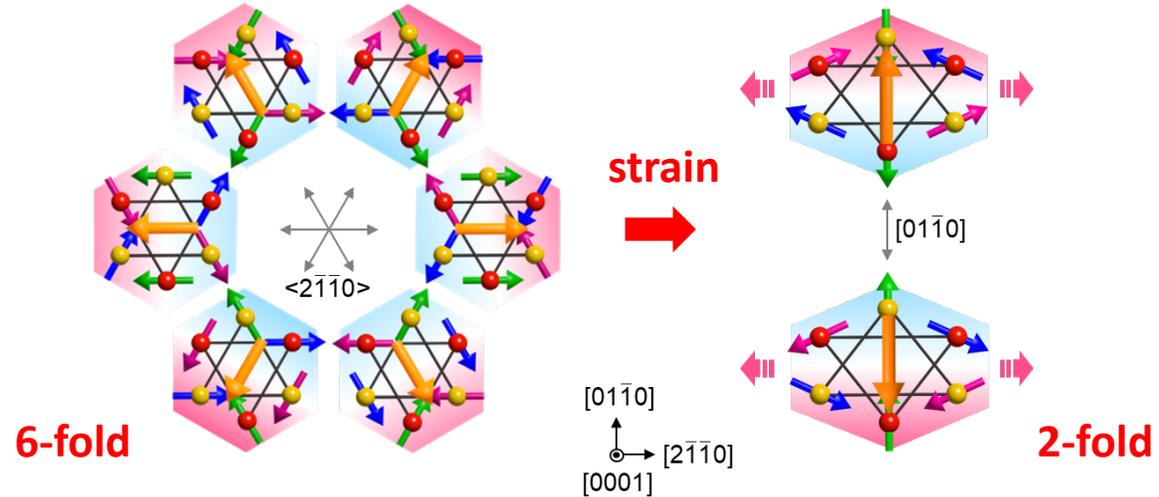
Mechanism of current induced switching



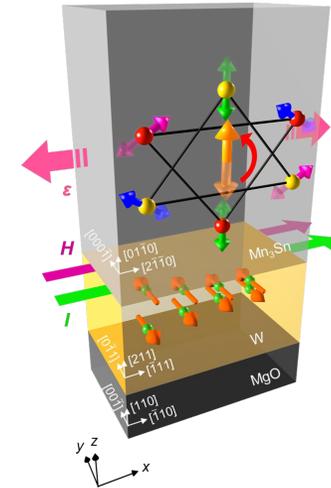
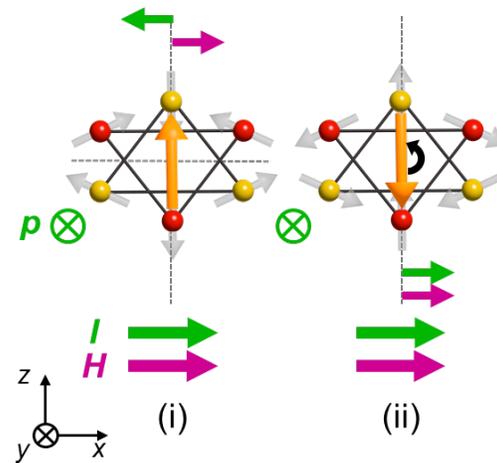
In-plane tensile strain stabilizes perpendicular magnetic anisotropy through piezomagnetic effect.

Spin current through SHE apply spin torque constructively to each sublattice.

Perpendicular magnetic anisotropy (PMA)



Current induced perpendicular switching



In-plane tensile strain can induce the perpendicular switching

Mechanism of current induced switching



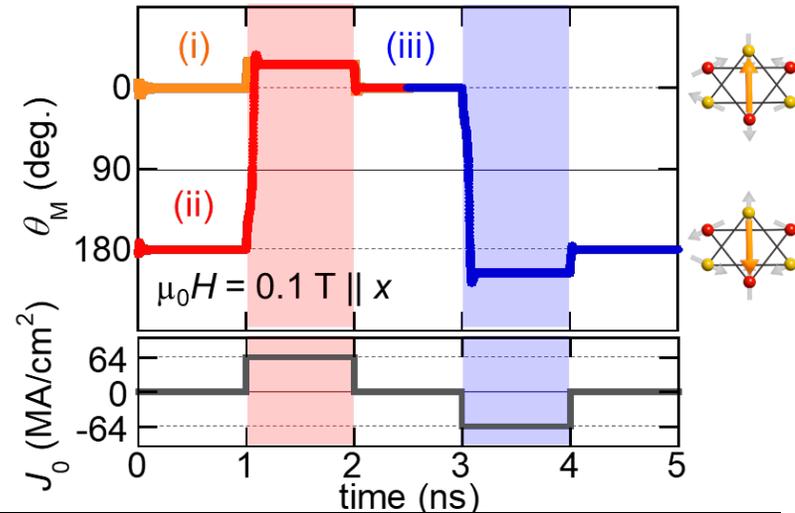
In-plane tensile strain stabilizes perpendicular magnetic anisotropy through piezomagnetic effect.

Spin current through SHE apply spin torque constructively to each sublattice.

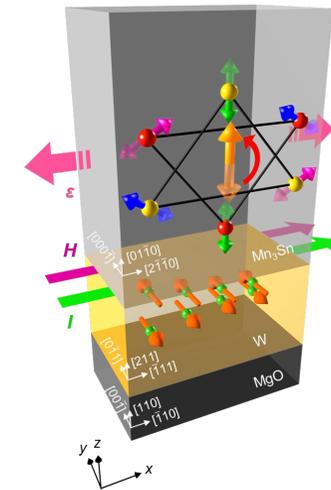
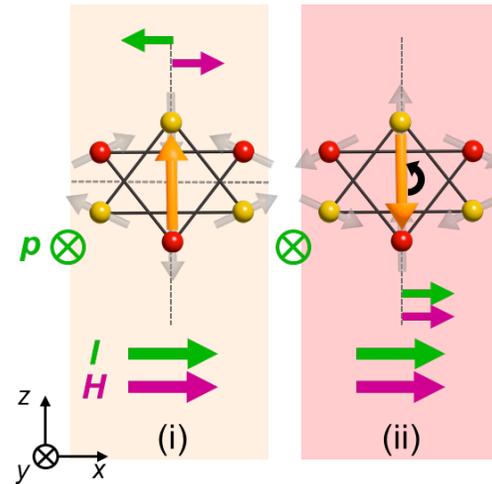
Change in current/field direction sets switching deterministically.

Efficient switching without intermediate state.

Numerical simulations



Current induced perpendicular switching



In-plane tensile strain can induce the perpendicular switching

$J_{\text{write}}^{\text{theory}} \sim 50 \text{ MA/cm}^2$ consistent with our observations

CSU PASM23 Summer School Lecture: Satoru Nakatsuji

Summary

- Giant Transverse Responses in Topological Magnetic Semimetals beyond the magnetization scaling.
- First Strain Control of Sign of AHE in Antiferromagnet by Large Piezomagnetism of Mn₃Sn
- First Full Electrical Control and Readout of AF Weyl semimetallic state
Writing: Four Terminal SOT Switching of AF State
Reading: AFM Tunneling Magnetoresistance

